

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	14	("4983544") or ("5783486") or ("6251711") or ("6316323") or ("6440851") or ("6627527") or ("66577244") or ("20030222320").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/05 13:23
S2	1916	stress and bridging and void	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:18
S3	69331	silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:18
S4	76	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:18
S5	3	("6410429").URPN.	USPAT	OR	ON	2005/09/05 10:33
S6	10	("5047367" "5194405" "5449642" "5536684" "5567652" "5728625" "5731239" "5766997" "5924010" "5970370").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/05 10:39
S7	321	cobalt adj disilicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:28
S8	35770	titanium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:39
S9	105	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:39
S10	1	("6388327").URPN.	USPAT	OR	ON	2005/09/05 10:56

S11	29	("5970370").URPN.	USPAT	OR	ON	2005/09/05 11:00
S12	0	co/tin/co	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:19
S13	0	"cosi2/tin/co"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:19
S14	0	"cosi2/ti/co"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:20
S15	0	(cobalt adj disilicide near3 titanium adj nitride) adj cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:21
S16	16	cobalt adj capping adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:23
S17	2	cobalt adj wiring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:08
S18	3017	compressive and tensile and cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:08
S19	516928	titanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09

S20	1978	S18 and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09
S21	69331	silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09
S22	268	S20 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09
S23	5	cobalt adj disilicide and (delamination or delaminate or delaminated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:29
S24	179952	compressive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23
S25	345187	tensile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23
S26	665844	laminate or laminated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23
S27	6666	S24 and S25 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23

S28	249294	cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:24
S29	630	S27 and S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:24
S30	85312	titanium and nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:24
S31	175	S29 and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:30
S32	2820	critical adj thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:30
S33	35920	delamination	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:30
S34	78	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:33
S35	16	cobalt adj cap adj layer or cobalt adj cap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:33

S36	249294	cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:32
S37	116168	(densification or dimensional adj reduction or volumetric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:33
S38	7608	S36 and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:33
S39	128110	cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:33
S40	179	S38 and S39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:41
S41	1108	titanium adj nitride and capping adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:41
S42	273	S36 and S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:41
S43	1	("6462390").URPN.	USPAT	OR	ON	2005/09/05 15:15
S44	7	("6281102").URPN.	USPAT	OR	ON	2005/09/05 15:24
S45	264	second adj cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 15:24

S46	509984	tin or titanium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 15:25
S47	53	S45 and S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 15:25
S48	5	("6207563").URPN.	USPAT	OR	ON	2005/09/05 15:54
S49	172871	consume or consumed or comsumption	USPAT	OR	ON	2005/09/05 15:55
S50	0	sacrificial adj cobalt	USPAT	OR	ON	2005/09/05 15:55
S51	11109	S36 and S49	USPAT	OR	ON	2005/09/05 15:55
S52	684	S39 and S51	USPAT	OR	ON	2005/09/05 15:55
S53	408	S46 and S52	USPAT	OR	ON	2005/09/05 15:56
S54	301902	cap or capping	USPAT	OR	ON	2005/09/05 15:56
S55	107	S54 and S53	USPAT	OR	ON	2005/09/05 15:56
S56	0	("6743721").URPN.	USPAT	OR	ON	2005/09/05 16:00
S57	30	("4885134" "4920073" "5047367" "5282946" "5302552" "5344793" "5356837" "5451545" "5536684" "5567651" "5728279" "5736461" "5747373" "5780362" "5824588" "5904564" "5970370" "5989988" "6022457" "6022795" "6025274" "6083817" "6100191" "6190516" "6251780" "6323130" "6376373" "6413859" "6440851" "6444578").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/05 16:00
S58	2	("6207563").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/05 16:35

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| <u>NEWS</u> | <u>3</u> | FEB 28 PATDPAFULL - New display fields provide for legal status data from INPADOC |
| <u>NEWS</u> | <u>4</u> | FEB 28 BABS - Current-awareness alerts (SDIs) available |
| <u>NEWS</u> | <u>5</u> | MAR 02 GBFULL: New full-text patent database on STN |
| <u>NEWS</u> | <u>6</u> | MAR 03 REGISTRY/ZREGISTRY - Sequence annotations enhanced |
| <u>NEWS</u> | <u>7</u> | MAR 03 MEDLINE file segment of TOXCENTER reloaded |
| <u>NEWS</u> | <u>8</u> | MAR 22 KOREAPAT now updated monthly; patent information enhanced |
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| <u>NEWS</u> | <u>10</u> | MAR 22 PATDPASPC - New patent database available |
| <u>NEWS</u> | <u>11</u> | MAR 22 REGISTRY/ZREGISTRY enhanced with experimental property tags |
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| <u>NEWS</u> | <u>13</u> | APR 04 EMBASE - Database reloaded and enhanced |
| <u>NEWS</u> | <u>14</u> | APR 18 New CAS Information Use Policies available online |
| <u>NEWS</u> | <u>15</u> | APR 25 Patent searching, including current-awareness alerts (SDIs), based on application date in CA/CAplus and USPATFULL/USPAT2 may be affected by a change in filing date for U.S. applications. |
| <u>NEWS</u> | <u>16</u> | APR 28 Improved searching of U.S. Patent Classifications for U.S. patent records in CA/CAplus |
| <u>NEWS</u> | <u>17</u> | MAY 23 GBFULL enhanced with patent drawing images |
| <u>NEWS</u> | <u>18</u> | MAY 23 REGISTRY has been enhanced with source information from CHEMCATS |
| <u>NEWS</u> | <u>19</u> | JUN 06 The Analysis Edition of STN Express with Discover! (Version 8.0 for Windows) now available |
| <u>NEWS</u> | <u>20</u> | JUN 13 RUSSIAPAT: New full-text patent database on STN |
| <u>NEWS</u> | <u>21</u> | JUN 13 FRFULL enhanced with patent drawing images |
| <u>NEWS</u> | <u>22</u> | JUN 27 MARPAT displays enhanced with expanded G-group definitions and text labels |
| <u>NEWS</u> | <u>23</u> | JUL 01 MEDICONF removed from STN |
| <u>NEWS</u> | <u>24</u> | JUL 07 STN Patent Forums to be held in July 2005 |
| <u>NEWS</u> | <u>25</u> | JUL 13 SCISEARCH reloaded |
| <u>NEWS</u> | <u>26</u> | JUL 20 Powerful new interactive analysis and visualization software, STN AnaVist, now available |
| <u>NEWS</u> | <u>27</u> | AUG 11 Derwent World Patents Index(R) web-based training during August |
| <u>NEWS</u> | <u>28</u> | AUG 11 STN AnaVist workshops to be held in North America |
| <u>NEWS</u> | <u>29</u> | AUG 30 CA/CAplus -Increased access to 19th century research documents |
| <u>NEWS</u> | <u>30</u> | AUG 30 CASREACT - Enhanced with displayable reaction conditions |
| <u>NEWS EXPRESS</u> | | JUNE 13 CURRENT WINDOWS VERSION IS V8.0, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 13 JUNE 2005 |
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=> s cobalt disilicide
 62465 COBALT
 1292 DISILICIDE
 L4 155 COBALT DISILICIDE
 (COBALT(W)DISILICIDE)

=> s titanium nitride
 87724 TITANIUM
 31667 NITRIDE
 L5 2294 TITANIUM NITRIDE
 (TITANIUM(W)NITRIDE)

=> s cobalt
 L6 62465 COBALT

=> s 14 and 15 and 16
 L7 0 L4 AND L5 AND L6

=> s 14 and 15
 L8 0 L4 AND L5

=> s tensile
 L9 57275 TENSILE

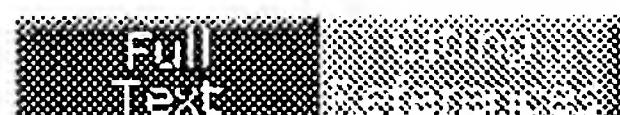
=> s compressive
 L10 24399 COMPRESSIVE

=> s silicide
 L11 8718 SILICIDE

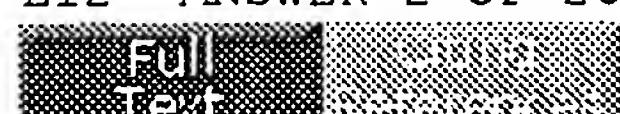
=> s 19 and 110 and 111
 L12 28 L9 AND L10 AND L11

=> d 112 1-28

L12 ANSWER 1 OF 28 INSPEC (C) 2005 IEE on STN

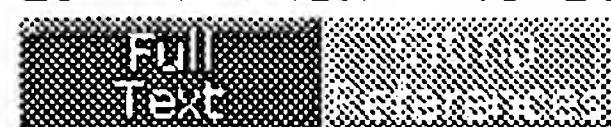

 AN 2004:8335912 INSPEC DN B2005-05-2530F-008
 TI Nanometer scale characterisation of CoSi₂ and NiSi induced strain in Si by convergent beam electron diffraction.
 AU Benedetti, A.; Bender, H.; Torregiani, C. (IMEC, Leuven, Belgium); Van Dal, M.; Maex, K.
 SO Materials Science & Engineering B (Solid-State Materials for Advanced Technology) (15 Dec. 2004) vol.B114-115, p.61-6. 11 refs.
 Published by: Elsevier
 Price: CCCC 0921-5107/04/\$30.00
 CODEN: MSBTEK ISSN: 0921-5107
 SICI: 0921-5107(20041215)B114:115L.61:NSCC;1-K
 Conference: EMRS 2004, Symposium B Material Science Issues in Advanced CMOS Source-Drain Engineering. Strasbourg, France, 2004
 DT Conference Article; Journal
 TC Experimental
 CY Switzerland
 LA English

L12 ANSWER 2 OF 28 INSPEC (C) 2005 IEE on STN



AN 2004:8271709 INSPEC DN A2005-06-8115C-014
 TI Preparation and properties of sputtered nitrogen-doped cobalt silicide film.
 AU Jyh-Hua Ting (Nat. Nano Device Labs., Hsinchu, Taiwan); Shiuann-Huah Shiau; Yeong-Jyh Chen; Fu-Ming Pan; Harianto Wang; Pu, G.M.; Chung-Yuan Kung
 SO Thin Solid Films (1 Dec. 2004) vol.468, no.1-2, p.155-60. 15 refs.
 Published by: Elsevier
 Price: CCCC 0040-6090/2004/\$30.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(20041201)468:1/2L.155:PPSN;1-L
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L12 ANSWER 3 OF 28 INSPEC (C) 2005 IEE on STN


 AN 2004:8223628 INSPEC DN A2005-03-7755-004; B2005-02-2810-011
 TI PLD of high-k dielectric films on silicon.
 AU Ratzke, M.; Kappa, M. (LS Experimentalphys. II, BTU Cottbus, Germany); Wolfframm, D.; Kouteva-Argirova, S.; Reif, J.
 SO Proceedings of the SPIE - The International Society for Optical Engineering (2004) vol.5662, no.1, p.406-11. 14 refs.
 Published by: SPIE-Int. Soc. Opt. Eng
 Price: CCCC 0277-786X/04/\$15.00
 CODEN: PSISDG ISSN: 0277-786X
 SICI: 0277-786X(2004)5662:1L.406:HDFS;1-M
 Conference: Fifth International Symposium on Laser Precision Microfabrication. Nara, Japan, 11-14 May 2004
 Sponsor(s): U.S. Air Force Office of Sci. Res., Asian Office of Aerospace Res. and Dev. (U.S. AFOSR/AOARD); Nara Convention Bur. (Japan); AIST - Nat. Inst. of Adv. Ind. Sci. and Technol. (Japan); Asahi Glass Found. for Promotion of Material Sci. and Technol. of Japan (Japan); Kao Found. for Arts and Sci. (Japan)
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

L12 ANSWER 4 OF 28 INSPEC (C) 2005 IEE on STN


 AN 2003:7643197 INSPEC DN A2003-13-6822-043; B2003-07-2530D-007
 TI Effects of stress on the interfacial reactions of metal thin films on (001)Si.
 AU Cheng, S.L.; Lo, H.M.; Cheng, L.W.; Chang, S.M.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan)
 SO Thin Solid Films (22 Jan. 2003) vol.424, no.1, p.33-9. 17 refs.
 Doc. No.: S0040-6090(02)00902-1
 Published by: Elsevier
 Price: CCCC 0040-6090/2003/\$30.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(20030122)424:1L.33:ESIR;1-R
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L12 ANSWER 5 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 2003:7613346 INSPEC DN A2003-12-6860-029; B2003-06-2550F-011
 TI Stress evolution in a Ti/Al(Si,Cu) dual layer during annealing.
 AU Bostrom, O.; Gergaud, P.; Thomas, O. (Lab. TECSEN, CNRS, Marseille, France); Boivin, P.
 SO Dislocations and Deformation Mechanisms in Thin Films and Small Structures (Material Research Society Symposium Proceedings Vol.673)
 Editor(s): Kraft, O.; Schwarz, K.W.; Baker, S.P.; Freund, L.B.; Hull, R. Warrendale, PA, USA: Mater. Res. Soc, 2001. p.P1.5.1-6 of xi+208 pp. 12 refs.
 Conference: San Francisco, CA, USA, 17-19 April 2001
 ISBN: 1-55899-609-5
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L12 ANSWER 6 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 2000:6596811 INSPEC DN B2000-06-2550F-094
 TI Silicide contacts for sub-0.25 μ m devices.
 AU Chen, L.J.; Cheng, S.L.; Chang, S.M.; Peng, Y.C.; Huang, H.Y.; Cheng, L.W. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan)
 SO Advanced Interconnects and Contacts. Symposium
 Editor(s): Edelstein, D.C.; Kikkawa, T.; Ozturk, M.C.; Tu, K.-N.; Weitzman, E.J. Warrendale, PA, USA: Mater. Res. Soc, 1999. p.123-34 of xiv+977 pp. 48 refs.
 Conference: San Francisco, CA, USA, 5-7 April 1999
 ISBN: 1-55899-471-8
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L12 ANSWER 7 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 2000:6544519 INSPEC DN B2000-05-2530D-011
 TI Characteristics of molybdenum nitride thin film by N₂+ ion implantation.
 AU Dong Joon Kim; Ik-Soo Kim; Yong Tae Kim (Semicond. Mater. Lab., Korea Inst. of Sci. & Technol., Seoul, South Korea); Jong-Wan Park
 SO Materials Reliability in Microelectronics IX. Symposium Warrendale, PA, USA: Mater. Res. Soc, 1999. p.45-50 of ix+311 pp. 6 refs.
 Conference: San Francisco, CA, USA, 6-8 April 1999
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

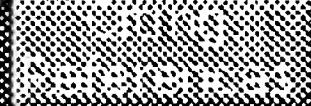
L12 ANSWER 8 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1999:6426396 INSPEC DN A2000-02-7340L-005; B2000-01-2530B-023
 TI Reduction of leakage current for shallow n+/p junction fabricated using C49 TiSi₂ as a diffusion source.
 AU Dong Kyun Sohn; Ji-Soo Park; Jong-Uk Bae; Byung Hak Lee; Chang Hee Han;

Jin Won Park (Div. of Res. & Dev., LG Semicon Co. Ltd., Cheongju, South Korea)
 SO Journal of the Electrochemical Society (Oct. 1999) vol.146, no.10,
 p.3837-42. 17 refs.
 Doc. No.: S0013-4651(99)01003-4
 Published by: Electrochem. Soc
 Price: CCCC 0013-4651/99/\$7.00
 CODEN: JESOAN ISSN: 0013-4651
 SICI: 0013-4651(199910)146:10L.3837:RLCS;1-7
 DT Journal
 TC Practical; Experimental
 CY United States
 LA English

L12 ANSWER 9 OF 28 INSPEC (C) 2005 IEE on STN

AN 1999:6319140 INSPEC DN A1999-18-6822-005; B1999-09-2530D-008
 TI The influences of stress on the growth of Ti and Ni silicide thin films
 on (001)Si.
 AU Chen, L.J.; Cheng, S.L.; Luo, H.M.; Huang, H.Y.; Peng, Y.C. (Dept. of
 Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Tsui, B.Y.;
 Tsai, C.J.; Guo, S.S.
 SO 1998 5th International Conference on Solid-State and Integrated Circuit
 Technology. Proceedings (Cat. No.98EX105)
 Editor(s): Zhang, M.; Tu, K.N.
 Piscataway, NJ, USA: IEEE, 1998. p.256-9 of xxi+973 pp. 6 refs.
 Conference: Beijing, China, 21-23 Oct 1998
 Sponsor(s): Chinese Inst. Electron.; IEEE Electron. Devices Soc.; IEEE
 Solid-State Circuits Soc.; Japan Soc. Appl. Phys.; URSI Comm. D; Electron.
 Div. IEEE (UK); Korea Inst. Telematics & Electron.; IEEE Beijing Sect
 Price: CCCC 0 7803 4306 9/98/\$10.00
 ISBN: 0-7803-4306-9
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L12 ANSWER 10 OF 28 INSPEC (C) 2005 IEE on STN

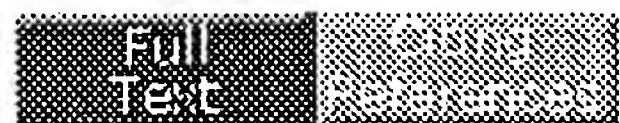
AN 1999:6196577 INSPEC DN A1999-09-6822-001; B1999-05-2550F-001
 TI Effects of stress on the growth of TiSi₂ thin films on (001)Si.
 AU Cheng, S.L.; Huang, H.Y.; Peng, Y.C.; Chen, L.J. (Dept. of Mater. Sci. &
 Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Tsui, B.Y.; Tsai, C.J.; Guo,
 S.S.
 SO Applied Physics Letters (8 March 1999) vol.74, no.10, p.1406-8. 9 refs.
 Doc. No.: S0003-6951(99)04910-4
 Published by: AIP
 Price: CCCC 0003-6951/99/74(10)/1406(3)/\$15.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(19990308)74:10L.1406:ESGT;1-D
 DT Journal
 TC Experimental
 CY United States
 LA English

L12 ANSWER 11 OF 28 INSPEC (C) 2005 IEE on STN

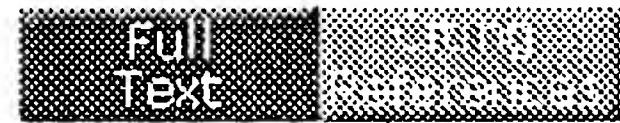
 

AN 1999:6191894 INSPEC DN B1999-04-2550F-040
 TI Effect of stress on **silicide** formation kinetics in thin film titanium-silicon system.
 AU Nagabushnam, R.V.; Singh, R.K. (Dept. of Mater. Sci. & Eng., Florida Univ., Gainesville, FL, USA); Sharan, S.
 SO Materials Science in Semiconductor Processing (1998) vol.1, no.3-4, p.249-55. 7 refs.
 Doc. No.: S1369-8001(98)00046-8
 Published by: Elsevier
 Price: CCCC 1369-8001/99/\$20.00
 CODEN: MSSPFQ ISSN: 1369-8001
 SICI: 1369-8001(1998)1:3/4L.249:ESSF;1-M
 Conference: E-MRS'98 Meeting. Symposium I: Rapid Thermal Processing. Strasbourg, France, 16-19 June 1998
 DT Conference Article; Journal
 TC Experimental
 CY United Kingdom
 LA English

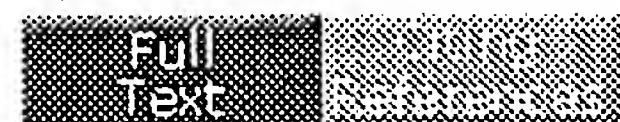
L12 ANSWER 12 OF 28 INSPEC (C) 2005 IEE on STN


 AN 1999:6134944 INSPEC DN B1999-02-2550F-075
 TI The effects of stress on the formation of titanium **silicide**.
 AU Cheng, S.L.; Huang, H.; Peng, Y.C.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Tsui, B.Y.; Tsai, C.J.; Guo, S.S.; Yu, K.H.
 SO Proceedings of the IEEE 1998 International Interconnect Technology Conference (Cat. No.98EX102)
 New York, NY, USA: IEEE, 1998. p.190-2 of 304 pp. 6 refs.
 Conference: San Francisco, CA, USA, 1-3 June 1998
 Sponsor(s): IEEE Electron Devices Soc
 Price: CCCC 0 7803 4285 2/98/\$10.00
 ISBN: 0-7803-4285-2
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L12 ANSWER 13 OF 28 INSPEC (C) 2005 IEE on STN

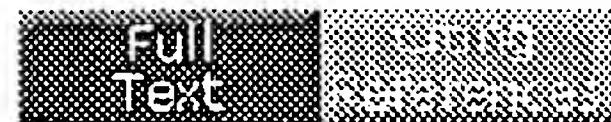

 AN 1996:5256554 INSPEC DN B9606-2550F-042
 TI Thermal stability of platinum **silicide** in deep sub-micron lines.
 AU Dan-Xia Xu; Das, S.R.; Erickson, L. (Inst. for Microstructural Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada); Naem, A.
 SO Materials Reliability in Microelectronics V. Symposium
 Editor(s): Oates, A.S.; Filter, W.F.; Rosenberg, R.; Greer, A.L.; Gadepally, K.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1995. p.223-8 of xv+523 pp. 4 refs.
 Conference: San Francisco, CA, USA, 17-21 April 1995
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L12 ANSWER 14 OF 28 INSPEC (C) 2005 IEE on STN

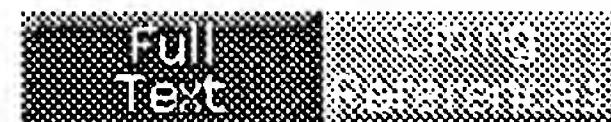

 AN 1995:5081171 INSPEC DN A9522-6822-018

TI Stress evolution during the growth of ultrathin layers of iron and iron silicide on Si(111).
AU Sander, D.; Enders, A.; Kirschner, J. (Max-Planck-Inst. fur Mikrostrukturphys., Halle, Germany)
SO Applied Physics Letters (25 Sept. 1995) vol.67, no.13, p.1833-5. 39 refs.
Price: CCCC 0003-6951/95/67(13)/1833/3/\$6.00
CODEN: APPLAB ISSN: 0003-6951
DT Journal
TC Experimental
CY United States
LA English

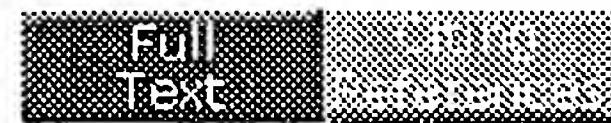
L12 ANSWER 15 OF 28 INSPEC (C) 2005 IEE on STN


AN 1995:4961282 INSPEC DN A9512-6855-041
TI Disordered structure of cubic iron silicide films on Si(111).
AU Whiteaker, K.L.; Robinson, I.K.; Benson, C. (Dept. of Phys., Illinois Univ., Urbana, IL, USA); Smilgies, D.M.; Onda, N.; von Kanel, H.
SO Physical Review B (Condensed Matter) (15 April 1995) vol.51, no.15, p.9715-21. 20 refs.
Price: CCCC 0163-1829/95/51(15)/9715(7)/\$06.00
CODEN: PRBMDO ISSN: 0163-1829
DT Journal
TC Experimental
CY United States
LA English

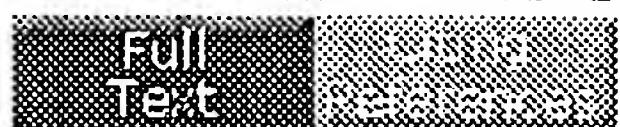
L12 ANSWER 16 OF 28 INSPEC (C) 2005 IEE on STN


AN 1994:4717874 INSPEC DN A9417-6855-024
TI Copper silicide precipitation influenced by the strain of a Ge0.02Si0.98 heteroepitaxial layer.
AU Kissinger, G.; Morgenstern, G.; Richter, H. (Inst. fur Halbleiterphys. Frankfurt (Oder) GmbH, Germany)
SO Journal of Applied Physics (15 May 1994) vol.75, no.10, pt.1, p.4994-5000. 15 refs.
Price: CCCC 0021-8979/94/75(10)/4994/7/\$6.00
CODEN: JAPIAU ISSN: 0021-8979
DT Journal
TC Experimental
CY United States
LA English

L12 ANSWER 17 OF 28 INSPEC (C) 2005 IEE on STN

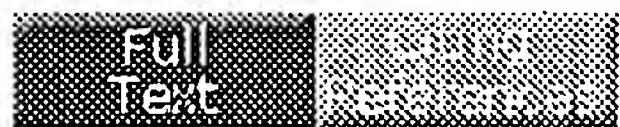

AN 1994:4636576 INSPEC DN B9405-2560R-025
TI The influence of mechanical stress on hot-carrier degradation in MOSFETs.
AU De Wolf, I.; Bellens, R.; Groeseneken, G.; Maes, H.E. (IMEC, Leuven, Belgium)
SO Materials Reliability in Microelectronics III Symposium
Editor(s): Rodbell, K.P.; Filter, W.F.; Frost, H.J.; Ho, P.S.
Pittsburgh, PA, USA: Mater. Res. Soc, 1993. p.281-6 of xi+496 pp. 14 refs.
Conference: San Francisco, CA, USA, 12-15 April 1993
DT Conference Article
TC Practical; Experimental
CY United States
LA English

L12 ANSWER 18 OF 28 INSPEC (C) 2005 IEE on STN



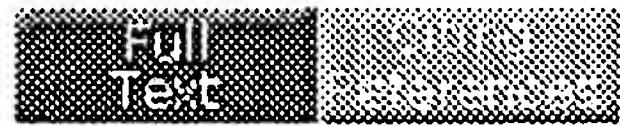
AN 1994:4620369 INSPEC DN A9408-6825-006; B9404-2530F-014
 TI Stress measurements in silicon substrates with TiSi₂ patterns using Raman microprobe.
 AU Ito, T.; Azuma, H.; Noda, S. (Toyota Central Res. & Dev. Labs. Inc., Aichi, Japan)
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers & Short Notes) (Jan. 1994) vol.33, no.1A, p.171-7. 14 refs.
 CODEN: JAPNDE ISSN: 0021-4922
 DT Journal
 TC Experimental
 CY Japan
 LA English

L12 ANSWER 19 OF 28 INSPEC (C) 2005 IEE on STN



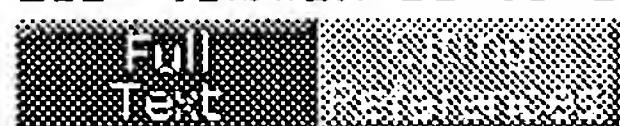
AN 1993:4484539 INSPEC DN A9321-6865-003
 TI Synthesis and properties of microlaminate structures by ion beam assisted deposition.
 AU Was, G.S.; Jones, J.W.; Kalnas, C.E.; Parfitt, L.J.; Mashayekhi, A. (Michigan Univ., Ann Arbor, MI, USA); Hoffmann, D.W.
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (June 1993) vol.B80-81, pt.2, p.1356-61. 18 refs.
 Price: CCCC 0168-583X/93/\$06.00
 CODEN: NIMBEU ISSN: 0168-583X
 Conference: Eighth International Conference on Ion Beam Modification of Materials. Heidelberg, Germany, 7-11 Sept 1992
 Sponsor(s): Anatech Ltd.; Bayer AG; Daimler-Benz AG; Danfysik A/S; et al
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L12 ANSWER 20 OF 28 INSPEC (C) 2005 IEE on STN



AN 1992:4161485 INSPEC DN A9213-6820-008
 TI Silicidation reaction and stress in Ti/Si.
 AU Chen, S.C.; Tamura, H. (VLSI R&D Center, Oki Electr. Ind. Co. Ltd., Tokyo, Japan); Hara, T.; Kinoshita, K.; Inoue, K.; Endo, N.; Nakamura, S.
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers & Short Notes) (Feb. 1992) vol.31, no.2A, p.201-5. 14 refs.
 CODEN: JAPNDE ISSN: 0021-4922
 DT Journal
 TC Experimental
 CY Japan
 LA English

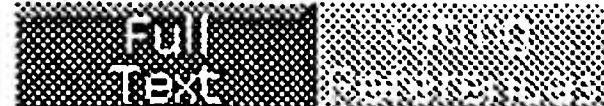
L12 ANSWER 21 OF 28 INSPEC (C) 2005 IEE on STN



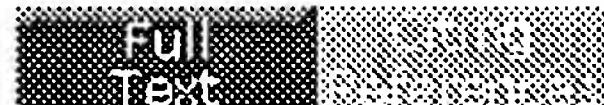
AN 1991:3990785 INSPEC DN A91135733
 TI Influence of particle bombardment on microstructure and internal stresses of refractory metal silicides on silicon.
 AU Hardtke, Ch.; Schilling, W.; Ullmaier, H. (Inst. fur Festkorperforschung,

SO Forschungszentrum Julich, Germany)
 Nuclear Instruments & Methods in Physics Research, Section B (Beam
 Interactions with Materials and Atoms) (July 1991) vol.B59-B60, pt.1,
 p.377-81. 11 refs.
 Price: CCCC 0168-583X/91/\$03.50
 CODEN: NIMBEU ISSN: 0168-583X
 Conference: 7th International Conference on Ion Beam Modification of
 Materials. Knoxville, TN, USA, 9-14 Sept 1990
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

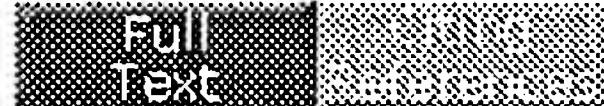
L12 ANSWER 22 OF 28 INSPEC (C) 2005 IEE on STN


 AN 1990:3725057 INSPEC DN A90132335
 TI Interfacial reaction of Ta- and Si-rich tantalum silicides with Si
 substrate.
 AU Hara, T.; Murota, M. (Dept. of Electr. Eng., Hosei Univ., Tokyo, Japan)
 SO Journal of Applied Physics (1 July 1990) vol.68, no.1, p.183-8. 23 refs.
 Price: CCCC 0021-8979/90/130183-06\$03.00
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L12 ANSWER 23 OF 28 INSPEC (C) 2005 IEE on STN


 AN 1990:3543735 INSPEC DN A90021439
 TI Stress relaxation in tantalum **silicide** films by particle bombardment.
 AU Hardtke, C.; Ullmaier, H.; Schilling, W.; Gebauer, M. (Inst. fur
 Festkorperforschung, KFA Julich, West Germany)
 SO Thin Solid Films (Aug. 1989) vol.175, p.61-5. 4 refs.
 Price: CCCC 0040-6090/89/\$3.50
 CODEN: THSFAP ISSN: 0040-6090
 Conference: 2nd International Symposium on Trends and New Applications in
 Thin Films (TATF 89). Regensburg, West Germany, 27 Feb-3 March 1989
 DT Conference Article; Journal
 TC Experimental
 CY Switzerland
 LA English

L12 ANSWER 24 OF 28 INSPEC (C) 2005 IEE on STN


 AN 1988:3074717 INSPEC DN A88034206
 TI Effect of substrate temperature on the properties of noncrystalline
 molybdenum **silicide** layers.
 AU Bretschneider, W.; Beddies, G.; Breuer, K.; Holzhuter, G.; Leimer, V.
 (Tech. Univ., Karl-Marx-Stadt, East Germany)
 SO Wissenschaftliche Zeitschrift der Technischen Universitaet Karl-Marx-Stadt
 (1987) vol.29, no.2, p.252-5. 10 refs.
 ISSN: 0863-0615
 DT Journal
 TC Experimental
 CY German Democratic Republic
 LA German

L12 ANSWER 25 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1987:3014592 INSPEC DN A87142848
 TI Stresses and radiation damage in Ar+ and Ti+ ion-implanted silicon.
 AU Madakson, P.; Angilello, J. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)
 SO Journal of Applied Physics (1 Sept. 1987) vol.62, no.5, p.1688-93. 14 refs.
 Price: CCCC 0021-8979/87/171688-06\$02.40
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L12 ANSWER 26 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1983:2103377 INSPEC DN A83091259
 TI Temperature effects on internal stress in molybdenum thin films on single-crystal silicon substrates.
 AU Jiann-Ruey Chen; Ching-Hung Ho (Dept. of Materials Sci. & Engng., Nat. Tsing Univ., Hsinchu, Taiwan)
 SO Thin Solid Films (17 June 1983) vol.104, no.1-2, p.251-5. 19 refs.
 Price: CCCC 0040-6090/83/\$3.00
 CODEN: THSFAP ISSN: 0040-6090
 Conference: Symposium on Interfaces and Contacts. Boston, MA, USA, 1-4 Nov 1982
 DT Conference Article; Journal
 TC Experimental
 CY Switzerland
 LA English

L12 ANSWER 27 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1975:799857 INSPEC DN A75061951
 TI Stresses in thin nickel silicide films.
 AU Koos, V.; Neumann, H.-G. (Sektion Phys. der Univ. Rostock, East Germany)
 SO Physica Status Solidi A (16 June 1975) vol.29, no.2, p.K115-16. 3 refs.
 CODEN: PSSABA ISSN: 0031-8965
 DT Journal
 TC Experimental
 CY German Democratic Republic
 LA English

L12 ANSWER 28 OF 28 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1971:256416 INSPEC DN A71033394
 TI Effect of copper on mechanical properties, machinability, corrosion behaviour and structural stability of calcium silicide inoculated cast irons.
 AU Krishna, L. (Univ. Roorkee, India); Gaindhar, J.L.
 SO Roorkee University Research Journal (1970) vol.12, no.1-2, p.39-43
 CODEN: RURJAX ISSN: 0557-3254
 DT Journal
 TC Experimental

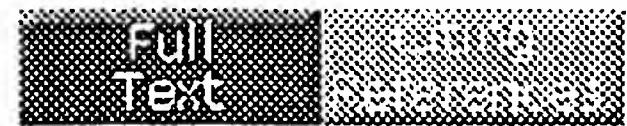
CY India
 LA English

=> s 19 and 110
 L13 7557 L9 AND L10

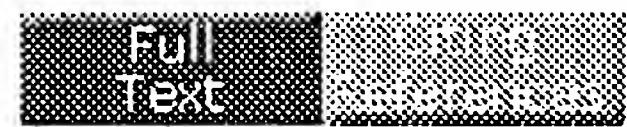
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 L14 0 L4 AND L13

=> d 14 1-155

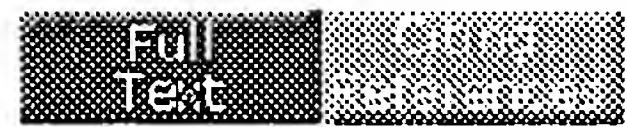
L4 ANSWER 1 OF 155 INSPEC (C) 2005 IEE on STN


 AN 2005:8518110 INSPEC DN A2005-18-8140G-010
 TI Effect of annealing on CoSi₂ thin films prepared by magnetron sputtering.
 AU Fanxiong Cheng; Chuanhai Jiang; Jiansheng Wu (Sch. of Mater. Sci. & Eng., Shanghai Jiao Tong Univ., China)
 SO Materials Science & Engineering B (Solid-State Materials for Advanced Technology) (15 May 2005) vol.119, no.1, p.61-4. 19 refs.
 Doc. No.: S0921-5107(05)00047-4
 Published by: Elsevier
 CODEN: MSBTEK ISSN: 0921-5107
 SICI: 0921-5107(20050515)119:1L.61:EACT;1-R
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 2 OF 155 INSPEC (C) 2005 IEE on STN

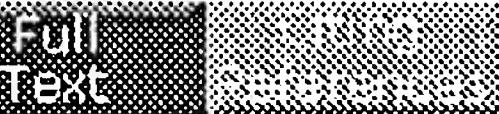

 AN 2005:8437942 INSPEC DN A2005-14-6848-004
 TI Real structure of the CoSi₂/Si(001) interface studied by dedicated aberration-corrected scanning transmission electron microscopy.
 AU Falke, M.; Falke, U.; Bleloch, A. (Daresbury Lab., UK); Teichert, S.; Beddies, G.; Hinneberg, H.-J.
 SO Applied Physics Letters (16 May 2005) vol.86, no.20, p.203103-1-3. 19 refs.
 Doc. No.: S0003-6951(05)07920-9
 Published by: AIP
 Price: CCCC 0003-6951/2005/86(20)/01/01/6495(3) /\$22.50
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(20050516)86:20L.203103:RSCI;1-E
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 3 OF 155 INSPEC (C) 2005 IEE on STN

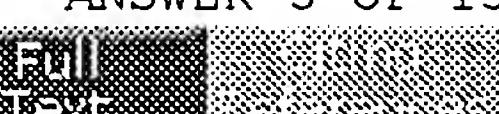

 AN 2005:8394414 INSPEC DN B2005-06-1265D-050; C2005-06-5320G-024
 TI Aggressively scaled (0.143 μm²) 6T-SRAM cell for the 32 nm node and beyond.
 AU Fried, D.M. (Syst. & Technol. Group, IBM Semicond. R&D Center, Hopewell Junction, NY, USA); Hergenrother, J.M.; Topol, A.W.; Chang, L.; Sekaric, L.; Sleigh, J.W.; McNab, S.J.; Newbury, J.; Steen, S.E.; Gibson, G.; Zhang, Y.; Fuller, N.C.M.; Bucchignano, J.; Lavoie, C.; Cabral Jr, C.;

Canaperi, D.; Dokumaci, O.; Frank, D.J.; Duch, E.A.; Babich, I.; Wong, K.; Ott, J.A.; Adams, C.D.; Dalton, T.J.; Nunes, R.; Medeiros, D.R.; Viswanathan, R.; Ketchen, M.; Ieong, M.; Haensch, W.; Guarini, K.W.
 SO 2004 International Electron Devices Meeting (IEEE Cat. No.04CH37602)
 Piscataway, NJ, USA: IEEE, 2005. p.261-4 of 1085 pp. 8 refs.
 Conference: San Francisco, CA, USA, 13-15 Dec 2004
 Price: CCCC 0 7803 8684 1/2004/\$20.00
 ISBN: 0-7803-8684-1
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 4 OF 155 INSPEC (C) 2005 IEE on STN


 AN 2004:8314823 INSPEC DN A2005-08-8115H-028; B2005-04-0520B-010
 TI Growth of epitaxial CoSi₂ from cobalt carbonyl on Si(100) substrate.
 AU Singanamalla, R.; Greve, D.W.; Barmak, K. (Dept. of Electr. & Comput. Eng., Carnegie Mellon Univ., Pittsburgh, PA, USA)
 SO Silicon Front-End Junction Formation-Physics and Technology (Materials Research Society Symposium Proceedings Vol.810)
 Editor(s): Pichler,P.; Claverie,A.; Lindsay,R.; Orlowski,M.; Windl,W. Warrendale, PA, USA: Materials Research Society, 2004. p.171-6 of xvi+494 pp. 10 refs.
 Conference: San Francisco, CA, USA, 13-15 April 2004
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 5 OF 155 INSPEC (C) 2005 IEE on STN

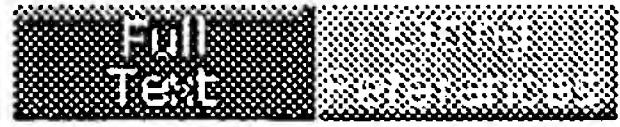

 AN 2004:8198371 INSPEC DN A2005-01-6855-077; B2005-01-0520F-067
 TI Structural and electrical characteristics of epitaxial CoSi₂ grown on n-Si_{0.83}Ge_{0.17}/n-Si(001) by reactive chemical vapor deposition using a Si capping layer.
 AU Shin, D.O.; Ban, S.H.; Ahn, Y.S.; Lee, Y.S.; Lee, N.-E. (Dept. of Mater. Eng., Sungkyunkwan Univ., Suwon, South Korea); Shim, K.-H.
 SO Thin Solid Films (30 June 2004) vol.458, no.1-2, p.269-73. 15 refs.
 Published by: Elsevier
 Price: CCCC 0040-6090/2004/\$30.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(20040630)458:1/2L.269:SECE;1-L
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 6 OF 155 INSPEC (C) 2005 IEE on STN

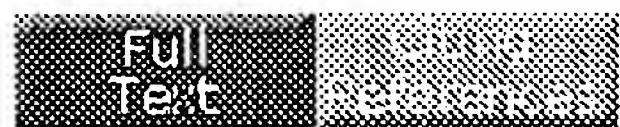

 AN 2004:8129899 INSPEC DN A2004-22-6848-001; B2004-11-2520C-006
 TI Nickel disilicide/silicon(001) interface structure revealed by HAADF in an aberration corrected dedicated STEM.
 AU Falke, U.; Falke, M.; Bleloch, A. (SuperSTEM, Daresbury Lab., UK)
 SO Microscopy and Microanalysis (2003) vol.9, suppl.3, p.288-9. 8 refs.
 Published by: Springer-Verlag
 CODEN: MIMIF7 ISSN: 1431-9276

SICI: 1431-9276(2003)9+3L.288:NDSI;1-O
 Conference: MC 2003. 31st Microscopy Conference-International Forum for Advanced Microscopy. Dresden, Germany, 7-12 Sept 2003
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

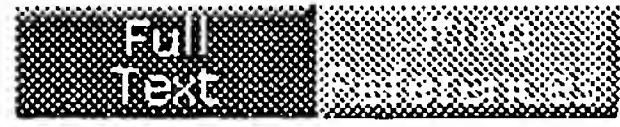
L4 ANSWER 7 OF 155 INSPEC (C) 2005 IEE on STN

 [Full Text]
 AN 2004:7944385 INSPEC DN B2004-06-2560R-016
 TI Experimental study of transport in nanoscale planar MOSFETs near the ballistic limit.
 AU Boeuf, F. (STMicroelectronics, Crolles, France); Jehl, X.; Sanquer, M.; Skotnicki, T.
 SO IEEE Transactions on Nanotechnology (March 2004) vol.3, no.1, p.105-9. 15 refs.
 Published by: IEEE
 Price: CCCC 1536-125X/04/\$20.00
 CODEN: ITNECU ISSN: 1536-125X
 SICI: 1536-125X(200403)3:1L.105:ESTN;1-C
 DT Journal
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 8 OF 155 INSPEC (C) 2005 IEE on STN

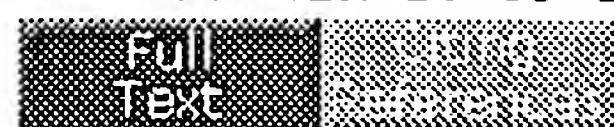
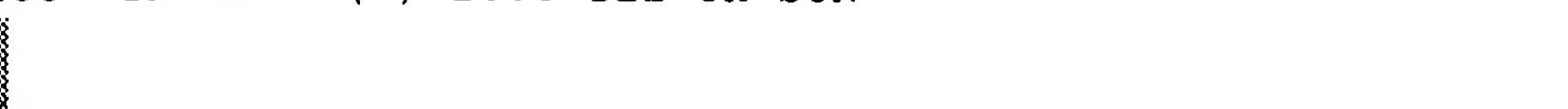
 [Full Text]
 AN 2004:7882082 INSPEC DN A2004-07-6170T-012; B2004-04-2550B-018
 TI Evolution of CoSi₂ buried structures created by high temperature Co⁺ ion implantation into Si(100) during post-implantation annealing.
 AU Hul'ko, O. (Dept. of Mater. Sci. & Eng., California Univ., Los Angeles, CA, USA); Zinke-Allmang, M.
 SO Surface Science (10 Dec. 2003) vol.547, no.1-2, p.219-28. 17 refs.
 Published by: Elsevier
 Price: CCCC 0039-6028/2003/\$30.00
 CODEN: SUSCAS ISSN: 0039-6028
 SICI: 0039-6028(20031210)547:1/2L.219:ECBS;1-A
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 9 OF 155 INSPEC (C) 2005 IEE on STN

 [Full Text]
 AN 2004:7842954 INSPEC DN A2004-05-8115H-015
 TI UHV/CVD growth of Co on Si(001) using cobalt carbonyl.
 AU Zhao, Q.; Greve, D.W. (Dept. of Electr. & Comput. Eng., Carnegie Mellon Univ., Pittsburgh, PA, USA); Barmark, K.
 SO Applied Surface Science (15 Oct. 2003) vol.219, no.1-2, p.136-42. 18 refs.
 Published by: Elsevier
 Price: CCCC 0169-4332/03/\$30.00
 CODEN: ASUSEE ISSN: 0169-4332
 SICI: 0169-4332(20031015)219:1/2L.136:GUCC;1-G
 Conference: Applied Surface Modeling: Experiment, Theory and Simulations. Cleveland, OH, USA, 21-23 Aug 2002
 DT Conference Article; Journal

TC Experimental
 CY Netherlands
 LA English

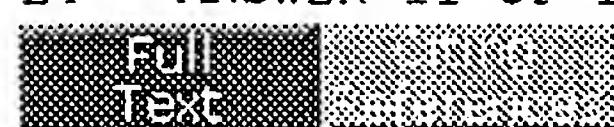
L4 ANSWER 10 OF 155 INSPEC (C) 2005 IEE on STN

AN 2003:7747512 INSPEC DN A2003-22-6865-007
 TI Bias voltage influence on the shape of cobalt-silicide nanowires.
 AU Palasantzas, G. (Dept. of Appl. Phys., Groningen Univ., Netherlands)
 SO Solid State Communications (2003) vol.127, no.3, p.219-22. 15 refs.
 Published by: Elsevier
 Price: CCCC 0038-1098/03/\$30.00
 CODEN: SSCOAA ISSN: 0038-1098
 SICI: 0038-1098(2003)127:3L.219:BVIS;1-U

DT Journal
 TC Experimental
 CY United States
 LA English

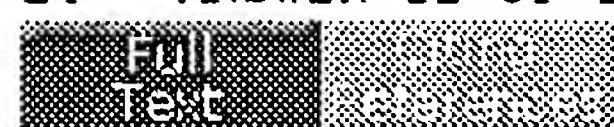
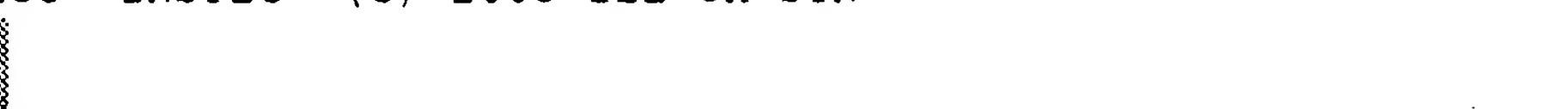
L4 ANSWER 11 OF 155 INSPEC (C) 2005 IEE on STN

AN 2003:7665633 INSPEC DN A2003-15-8160C-066; B2003-08-2550E-046
 TI Cleaning after contact etching of multi-film stack and **cobalt disilicide**: an XPS study.
 AU Chooi, S.Y.M.; Lim, C.; Liu, W.-J.; Ee, P.-Y. (Adv. Module Technol. Div., Chartered Semicond. Manuf., Singapore, Singapore)
 SO Diffusion and Defect Data Part B (Solid State Phenomena) (2003) vol.92, p.243-6. 2 refs.
 Published by: Balaban Publishers; Scitec Publications
 CODEN: DDBPE8 ISSN: 1012-0394
 SICI: 1012-0394(2003)92L.243:CACE;1-B

DT Journal
 TC Experimental
 CY Switzerland
 LA English

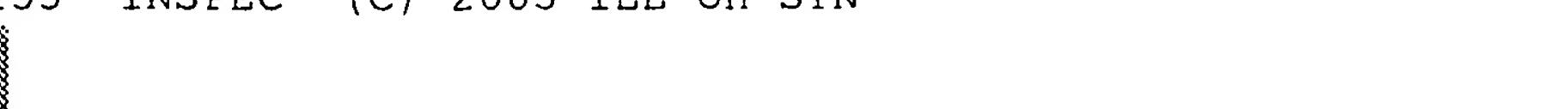
L4 ANSWER 12 OF 155 INSPEC (C) 2005 IEE on STN

AN 2003:7645274 INSPEC DN B2003-07-2550F-006
 TI Picosecond ultrasonics provides CoSi characterization.
 AU Tas, G.; Morath, C. (Rudolph Technol. Inc., USA); Stoner, R.; Lavoie, C.; Cabral, C., Jr.; Harper, J.; Yaw-Lin Huang; Huang, D.; Ren Chen
 SO Semiconductor International (Feb. 2003) vol.26, no.2, p.70-4. 10 refs.
 Published by: Cahners Publishing
 CODEN: SITLDD ISSN: 0163-3767
 SICI: 0163-3767(200302)26:2L.70:PUPC;1-K

DT Journal
 TC Practical; Experimental
 CY United States
 LA English

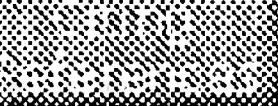
L4 ANSWER 13 OF 155 INSPEC (C) 2005 IEE on STN

AN 2003:7636700 INSPEC DN A2003-13-6855-158; B2003-06-2550B-094
 TI A self-aligned silicide process utilizing ion implants for reduced silicon consumption and control of the silicide formation temperature.

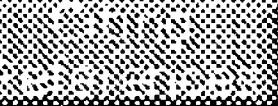
AU Cohen, G.M.; Cabral, C., Jr.; Lavoie, C.; Solomon, P.M.; Guarini, K.W.; Chan, K.K.; Roy, R.A. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)
 SO Silicon Materials - Processing, Characterization and Reliability Symposium (Mater. Res. Soc. Proceedings Vol. 716)
 Editor(s): Veteran, J.L.; O'Meara, D.L.; Misra, V.; Ho, P.S.
 Warrendale, PA, USA: Mater. Res. Soc, 2002. p.35-40 of xvii+672 pp. 6 refs.
 Conference: San Francisco, CA, USA, 1-5 April 2002
 ISBN: 1-55899-652-4
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 14 OF 155 INSPEC (C) 2005 IEE on STN

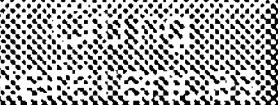
AN 2002:7456994 INSPEC DN A2003-01-8120V-014; B2003-01-0587-012
 TI The oriented growth of carbon nanotubes on Si(100).
 AU Rotkina, L.; Shah, S.; Choi, H.; Lyding, J.W. (Beckman Inst. for Adv. Sci. & Technol., Illinois Univ., Urbana, IL, USA)
 SO AIP Conference Proceedings (2001) no.591, p.247-50. 6 refs.
 Published by: AIP
 Price: CCCC 0094-243X/01/\$18.00
 CODEN: APCPCS ISSN: 0094-243X
 SICI: 0094-243X(2001)591L.247:OGCN;1-U
 Conference: Electronic Properties of Molecular Nanostructures: 15th International Winterschool/Euroconference. Kirchberg, Austria, 3-10 March 2001
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 15 OF 155 INSPEC (C) 2005 IEE on STN

AN 2002:7435224 INSPEC DN A2002-24-6855-014
 TI Initial stages of cobalt disilicide formation on silicon single crystals.
 AU Gomoyunova, M.V.; Pronin, I.I.; Valdaitsev, D.A.; Faradzhev, N.S. (A.F. Ioffe Phys. Tech. Inst., St. Petersburg, Russia); Luches, P.; Rota, A.; Valeri, S.
 SO Physics of Low-Dimensional Structures (2002) no.3-4, p.163-76. 31 refs.
 Published by: VSV Co. Ltd
 CODEN: PLDSFC ISSN: 0204-3467
 SICI: 0204-3467(2002)3/4L.163:ISCD;1-1
 DT Journal
 TC Experimental
 CY Russian Federation
 LA English

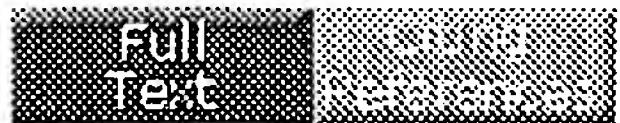
L4 ANSWER 16 OF 155 INSPEC (C) 2005 IEE on STN

AN 2002:7418663 INSPEC DN A2002-23-6170T-006; B2002-11-2550B-027
 TI Influence of ion implantation induced defects on formation of buried CoSi₂ structures in Si(100).
 AU Hul'ko, O. (Dept. of Phys. & Astron., Univ. of Western Ontario, London, Ont., Canada); Fraser, J.; Zinke-Allmang, M.

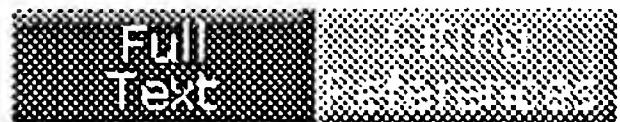
SO Thin Solid Films (24 June 2002) vol.413, no.1-2, p.52-8. 17 refs.
 Doc. No.: S0040-6090(02)00279-1
 Published by: Elsevier
 Price: CCCC 0040-6090/02/\$22.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(20020624)413:1/2L.52:IIID;1-L
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 17 OF 155 INSPEC (C) 2005 IEE on STN

 [REDACTED]

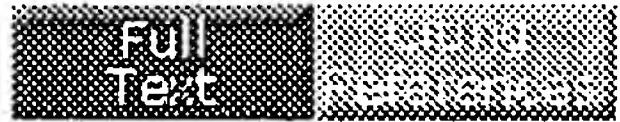
AN 2002:7363235 INSPEC DN A2002-20-6855-030; B2002-10-0520-002
 TI Reactive epitaxy of **cobalt disilicide** on Si(100).
 AU Gomoyunova, M.V.; Pronin, I.I.; Valdaitsev, D.A.; Faradzhev, N.S. (A.F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia)
 SO Physics of The Solid State (June 2002) vol.44, no.6, p.1176-80. 29 refs.
 Published by: MAIK Nauka
 Price: CCCC 1063-7834/02/4406-1176\$22.00
 CODEN: PSOSED ISSN: 1063-7834
 SICI (Trl): 1063-7834(200206)44:6L.1176:RECD;1-1
 Translation of: Fizika Tverdogo Tela (June 2002) vol.44, no.6, p.1126-30. 29 refs.
 CODEN: FTVTAC ISSN: 0367-3294
 SICI: 0367-3294(200206)44:6L.1126;1-V
 DT Journal; Translation Abstracted
 TC Experimental
 CY Russian Federation; Russian Federation
 LA English

L4 ANSWER 18 OF 155 INSPEC (C) 2005 IEE on STN

 [REDACTED]

AN 2002:7361117 INSPEC DN A2002-19-7360D-002; B2002-10-2520M-006
 TI A study on the polycrystalline silicon germanium gate electrode fabrication technology for cobalt silicide process.
 AU Sato, H.; Sukegawa, T.; Mori, T.; Suzuki, K.; Mori, H. (Manuf. Technol. Dev. Div., Fujitsu Ltd., Mie, Japan)
 SO Gate Stack and Silicide Issues in Silicon Processing II. Symposium (Materials Research Society Symposium Proceedings Vol.670)
 Editor(s): Campbell, S.A.; Clevenger, L.A.; Griffin, P.B.; Hobbs, C.C. Warrendale, PA, USA: Mater. Res. Soc, 2002. p.K5.10.1-6 of xi+262 pp. 4 refs.
 Conference: San Francisco, CA, USA, 17-19 April 2001
 ISBN: 1-55899-606-0
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

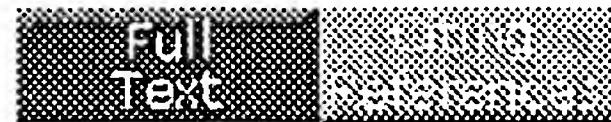
L4 ANSWER 19 OF 155 INSPEC (C) 2005 IEE on STN

 [REDACTED]

AN 2002:7297866 INSPEC DN A2002-15-6855-022
 TI Atomic level characterization of ultrathin flat **cobalt disilicide** film with three crystalline domains.
 AU Ohtomo, T.; Kawasaki, T.; Takai, Y. (Dept. of Material & Life Sci., Osaka Univ., Japan)

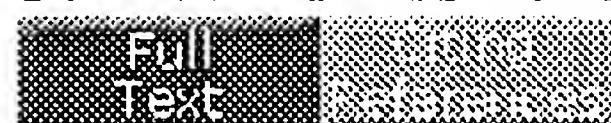
SO Journal of Applied Physics (15 June 2002) vol.91, no.12, p.9663-6. 18 refs.
 Doc. No.: S0021-8979(02)10812-7
 Published by: AIP
 Price: CCCC 0021-8979/2002/91(12)/9663(4)/\$19.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(20020615)91:12L.9663:ALCU;1-P
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 20 OF 155 INSPEC (C) 2005 IEE on STN

 [REDACTED]

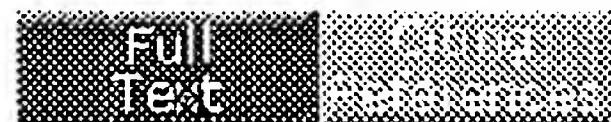
AN 2002:7136176 INSPEC DN A2002-03-7125P-006
 TI Electron momentum density distribution in **cobalt disilicide**: Analysis by the maximum entropy method.
 AU Bellin, Ch.; Dobrzynski, L.; Kouba, H.; Loupias, G. (LMCP, Paris VI Univ., France); Buslaps, T.; Honkimaki, V.
 SO Zeitschrift fur Physikalische Chemie (2001) vol.215, no.11, p.1367-87. 28 refs.
 Published by: Oldenbourg
 Price: CCCC 0942-9352/01/\$3.00
 CODEN: ZPCFAX ISSN: 0942-9352
 SICI: 0942-9352(2001)215:11L.1367:EMDD;1-V
 DT Journal
 TC Theoretical
 CY Germany, Federal Republic of
 LA English

L4 ANSWER 21 OF 155 INSPEC (C) 2005 IEE on STN

 [REDACTED]

AN 2001:6959674 INSPEC DN A2001-15-6630N-001
 TI Formation of Co-Si intermetallics in bulk diffusion couples. I. growth kinetics and mobilities of species in the silicide phases.
 AU Van Dal, M.J.H.; Huibers, D.G.G.M.; Kodentsov, A.A.; Van Loo, F.J.J. (Lab. for Solid State Chem. & Mater. Sci., Eindhoven Univ. of Technol., Netherlands)
 SO Intermetallics (2001) vol.9, no.5, p.409-21. 42 refs.
 Doc. No.: S0966-9795(01)00018-8
 Published by: Elsevier
 Price: CCCC 0966-9795/2001/\$20.00
 CODEN: IERME5 ISSN: 0966-9795
 SICI: 0966-9795(2001)9:5L.409:FIBD;1-V
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 22 OF 155 INSPEC (C) 2005 IEE on STN

 [REDACTED]

AN 2001:6945449 INSPEC DN A2001-14-6822-002
 TI XAFS studies of the formation of cobalt silicide on (square root 3* square root 3) SiC(0001).
 AU Platow, W.; Wood, D.E.; Burnette, J.E.; Nemanich, R.J.; Sayers, D.E. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)
 SO Journal of Synchrotron Radiation (1 March 2001) vol.8, pt.2, p.475-7. 5

refs.
 Published by: Munksgaard International Booksellers and Publishers for Int.
 Union Crystallogr
 CODEN: JSYRES ISSN: 0909-0495
 SICI: 0909-0495(20010301)8:2L.475:XSFC;1-V
 Conference: Eleventh International Conference on X-Ray Absorption Fine
 Structure. XAFS XI. Ako, Japan, 26-31 July 2000
 DT Conference Article; Journal
 TC Experimental
 CY Denmark
 LA English

L4 ANSWER 23 OF 155 INSPEC (C) 2005 IEE on STN

 
 AN 2001:6935589 INSPEC DN A2001-13-7960-005
 TI Theoretical photoemission and X-ray emission spectra of nickel and
cobalt disilicide films.
 AU Pereslavtseva, N.S.; Kurganskii, S.I. (Voronezh State Univ., Russia)
 SO Journal of Electron Spectroscopy and Related Phenomena (March 2001)
 vol.114-116, p.549-54. 19 refs.
 Doc. No.: S0368-2048(00)00345-5
 Published by: Elsevier
 Price: CCCC 0368-2048/2001/\$20.00
 CODEN: JESRAW ISSN: 0368-2048
 SICI: 0368-2048(200103)114/116L.549:TPES;1-9
 Conference: Eighth International Conference on Electronic Spectroscopy and
 Structure. Berkeley, CA, USA, 8-12 Aug 2000
 DT Conference Article; Journal
 TC Theoretical
 CY Netherlands
 LA English

L4 ANSWER 24 OF 155 INSPEC (C) 2005 IEE on STN

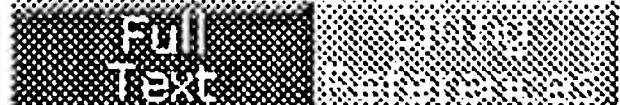
 
 AN 2001:6928258 INSPEC DN A2001-12-6855-065
 TI Formation of **cobalt disilicide** films on (square root 3* square root
 $3)$ 6H-SiC(0001).
 AU Platow, W.; Wood, D.K.; Tracy, K.M.; Burnette, J.E.; Nemanich, R.J.;
 Sayers, D.E. (Dept. of Phys., North Carolina State Univ., Raleigh, NC,
 USA)
 SO Physical Review B (Condensed Matter and Materials Physics) (15 March 2001)
 vol.63, no.11, p.115312/1-7. 25 refs.
 Doc. No.: S0163-1829(01)04307-7
 Published by: APS through AIP
 Price: CCCC 0163-1829/2001/63(11)/115312(7)/\$15.00
 CODEN: PRBMDO ISSN: 0163-1829
 SICI: 0163-1829(20010315)63:11L.1:FCDF;1-L
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 25 OF 155 INSPEC (C) 2005 IEE on STN

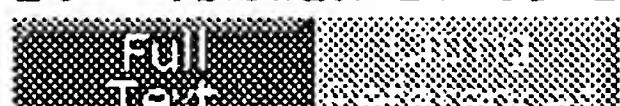
 
 AN 2001:6903035 INSPEC DN A2001-10-6855-098; B2001-05-0520D-031
 TI Reactive epitaxy of **cobalt disilicide** on Si(111).
 AU Gomoyunova, M.V.; Pronin, I.I.; Valdaitsev, D.A.; Faradzhev, N.S. (A.F.

SO Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia)
 Physics of The Solid State (March 2001) vol.43, no.3, p.569-73. 36 refs.
 Published by: MAIK Nauka
 Price: CCCC 1063-7834/2001/4303-0569\$21.00
 CODEN: PSOSED ISSN: 1063-7834
 SICI (Trl): 1063-7834(200103)43:3L.569:RECD;1-3
 Translation of: Fizika Tverdogo Tela (March 2001) vol.43, no.3, p.549-53.
 36 refs.
 CODEN: FTVTAC ISSN: 0367-3294
 SICI: 0367-3294(200103)43:3L.549;1-R
 DT Journal; Translation Abstracted
 TC Experimental
 CY Russian Federation; Russian Federation
 LA English

L4 ANSWER 26 OF 155 INSPEC (C) 2005 IEE on STN


 AN 2001:6893009 INSPEC DN A2001-10-6822-016; B2001-05-2550A-005
 TI Role of ripening and defects in the formation of mesotaxial
cobalt-disilicide layers.
 AU Hul'ko, O. (Dept. of Phys. & Astron., Univ. of Western Ontario, London,
 Ont., Canada); McCaffrey, J.P.; Zinke-Allmang, M.
 SO Ultramicroscopy (Jan. 2001) vol.86, no.1-2, p.39-48. 27 refs.
 Doc. No.: S0304-3991(00)00090-5
 Published by: Elsevier
 Price: CCCC 0304-3991/2001/\$20.00
 CODEN: ULTRD6 ISSN: 0304-3991
 SICI: 0304-3991(200101)86:1/2L.39:RRDF;1-9
 Conference: SPM 2000. Second International Conference on Scanning Probe
 Microscopy, Sensors and Nanostructures. Heidelberg, Germany, 28-31 May
 2000
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 27 OF 155 INSPEC (C) 2005 IEE on STN


 AN 2000:6754286 INSPEC DN B2000-12-2550F-115
 TI Thermal stability improvement of **cobalt disilicide** thin films on
 $(001)Si$ by high temperature sputtering deposition.
 AU Huang, H.Y.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua
 Univ., Hsinchu, Taiwan); Wu, W.F.; Yang, R.P.
 SO Advances in Rapid Thermal Processing. Proceedings of the Symposium.
 (Electrochemical Society Proceeding Vol.99-10)
 Editor(s): Roozeboom, F.; Gelpay, J.C.; Ozturk, M.; Nakos, J.
 Pennington, NJ, USA: Electrochem. Soc, 1999. p.257-61 of xii+452 pp. 9
 refs.
 Conference: Seattle, WA, USA, 3-6 May 1999
 Sponsor(s): Electrochem. Soc
 ISBN: 1-56677-232-X
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 28 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 2000:6718461 INSPEC DN A2000-21-7125T-004
 TI Electronic structure of cobalt disilicide film.
 AU Kurganskii, S.I.; Pereslavtseva, N.S. (Voronezh State Univ., Russia)
 SO Physics of The Solid State (Aug. 2000) vol.42, no.8, p.1542-7. 12 refs.
 Published by: MAIK Nauka
 Price: CCCC 1063-7834/2000/4208-1542\$20.00
 CODEN: PSOSED ISSN: 1063-7834
 SICI (Trl): 1063-7834(200008)42:8L.1542:ESCD;1-T
 Translation of: Fizika Tverdogo Tela (Aug. 2000) vol.42, no.8, p.1499-504.
 12 refs.
 CODEN: FTVTAC ISSN: 0367-3294
 SICI: 0367-3294(200008)42:8L.1499;1-4
 DT Journal; Translation Abstracted
 TC Theoretical
 CY Russian Federation; Russian Federation
 LA English

L4 ANSWER 29 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 2000:6672711 INSPEC DN B2000-09-2550F-030
 TI Study of capping layers, cleaning method, and rapid thermal processing temperature on cobalt silicide formation.
 AU Saigal, D.; Lai, G.; Yang, L.; Su, J.; Ngan, K.; Narasimhan, M.; Chen, F.;
 Singhal, A.; Lopes, D. (Appl. Mater. Inc., Santa Clara, CA, USA); Lian,
 S.; Cao, W.; Tsai, K.; Lo, P.; Lee, S.K.; Shih, J.
 SO Proceedings of the SPIE - The International Society for Optical Engineering (1999) vol.3883, p.84-95. 8 refs.
 Published by: SPIE-Int. Soc. Opt. Eng
 Price: CCCC 0277-786X/99/\$10.00
 CODEN: PSISDG ISSN: 0277-786X
 SICI: 0277-786X(1999)3883L.84:SCLC;1-R
 Conference: Multilevel Interconnect Technology III. Santa Clara, CA, USA,
 22-23 Sept 1999
 Sponsor(s): SPIE
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

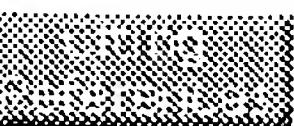
L4 ANSWER 30 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 2000:6596816 INSPEC DN B2000-06-2550F-099
 TI Formation and characterization of SPE grown ultra-thin cobalt disilicide film.
 AU Xin-Ping Qu (Dept. of Electron. Eng., Fudan Univ., Shanghai, China);
 Guo-Ping Ru; Bing-Zong Li; Detavernier, C.; Van Meirhaeghe, R.L.; Cardon,
 F.
 SO Advanced Interconnects and Contacts. Symposium
 Editor(s): Edelstein, D.C.; Kikkawa, T.; Ozturk, M.C.; Tu, K.-N.;
 Weitzman, E.J.
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.157-62 of xiv+977 pp. 12
 refs.
 Conference: San Francisco, CA, USA, 5-7 April 1999
 ISBN: 1-55899-471-8
 DT Conference Article
 TC Practical; Experimental

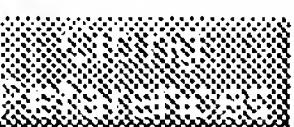
CY United States
 LA English

L4 ANSWER 31 OF 155 INSPEC (C) 2005 IEE on STN

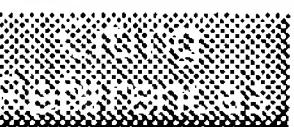
AN 2000:6496152 INSPEC DN A2000-06-6180J-004; B2000-03-2550B-019
 TI Radiation damage in focused ion beam implantation.
 AU Hausmann, S.; Bischoff, L.; Teichert, J.; Voelskow, M.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf eV, Germany)
 SO Digest of Papers. Microprocesses and Nanotechnology '99. 1999 International Microprocesses and Nanotechnology Conference Tokyo, Japan: Japan Society of Applied Physics, 1999. p.146-7 of xxii+234 pp. 4 refs.
 Conference: Yokohama, Japan, 6-8 July 1999
 Sponsor(s): Japan Soc. of Appl. Phys.; IEEE Electron Device Soc
 ISBN: 4-930813-97-2
 DT Conference Article
 TC Experimental
 CY Japan
 LA English

L4 ANSWER 32 OF 155 INSPEC (C) 2005 IEE on STN

AN 2000:6492138 INSPEC DN A2000-06-6822-004; B2000-03-2550F-030
 TI Effect of lateral dimensional scaling on the thermal stability of poly-CoSi₂ reacted on Si(001).
 AU Alberti, A. (INFM, Catania, Italy); La Via, F.; Ravesi, S.; Rimini, E.
 SO Microelectronic Engineering (Jan. 2000) vol.50, no.1-4, p.179-86. 15 refs.
 Doc. No.: S0167-9317(99)00280-4
 Published by: Elsevier
 Price: CCCC 0167-9317/2000/\$20.00
 CODEN: MIENEF ISSN: 0167-9317
 SICI: 0167-9317(200001)50:1/4L.179:ELDS;1-Q
 Conference: Third European Workshop on Materials for Advanced Metallization. Ostende, Belgium, 7-10 March 1999
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 33 OF 155 INSPEC (C) 2005 IEE on STN

AN 2000:6472583 INSPEC DN A2000-04-6170T-007; B2000-02-2550B-038
 TI Dwell-time related effects in focused ion beam synthesis of cobalt disilicide.
 AU Hausmann, S.; Bischoff, L.; Teichert, J.; Voelskow, M.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf, Dresden, Germany)
 SO Journal of Applied Physics (1 Jan. 2000) vol.87, no.1, p.57-62. 21 refs.
 Doc. No.: S0021-8979(90)03901-9
 Published by: AIP
 Price: CCCC 0021-8979/2000/87(1)/57(6)/\$15.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(20000101)87:1L.57:DTRE;1-O
 DT Journal
 TC Experimental

CY United States
 LA English

L4 ANSWER 34 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2000:6464472 INSPEC DN A2000-04-6475-001
 TI Germanium segregation in the Co/SiGe/Si(001) thin film system.
 AU Goeller, P.T.; Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA); Myers, A.F.; Steel, E.B.
 SO Journal of Materials Research (Nov. 1999) vol.14, no.11, p.4372-84. 57 refs.
 Published by: Mater. Res. Soc
 Price: CCCC 0884-2914/99/\$2.50
 CODEN: JMREEE ISSN: 0884-2914
 SICI: 0884-2914(199911)14:11L.4372:GSST;1-6
 DT Journal
 TC Bibliography; Experimental
 CY United States
 LA English

L4 ANSWER 35 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1999:6406812 INSPEC DN A1999-24-6170W-003; B1999-12-2530D-034
 TI Solid solubility of As in CoSi₂ and redistribution at the CoSi₂/Si interface.
 AU Mangelinck, D. (Inst. of Mater. Res. & Eng., Kent Ridge, Singapore); Cardenas, J.; d'Heurle, F.M.; Svensson, B.G.; Gas, P.
 SO Journal of Applied Physics (1 Nov. 1999) vol.86, no.9, p.4908-15. 38 refs.
 Doc. No.: S0021-8979(99)08121-9
 Published by: AIP
 Price: CCCC 0021-8979/99/86(9)/4908(8) /\$15.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(19991101)86:9L.4908:SSCR;1-S
 DT Journal
 TC Theoretical; Experimental
 CY United States
 LA English

L4 ANSWER 36 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1999:6406755 INSPEC DN A1999-24-7340N-013; B1999-12-2530D-032
 TI Abnormal junction leakage characteristics in titanium-capped cobalt disilicide.
 AU Chang-Yong Kang; Dae-Gwan Kang; Joo-Wan Lee (R&D Div., LG Semicon Co. Ltd., Cheongju, South Korea)
 SO Journal of Applied Physics (1 Nov. 1999) vol.86, no.9, p.5293-5. 10 refs.
 Doc. No.: S0021-8979(99)04821-5
 Published by: AIP
 Price: CCCC 0021-8979/99/86(9)/5293(3) /\$15.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(19991101)86:9L.5293:AJLC;1-V
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 37 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

FULL **TEX**

AN 1999:6360440 INSPEC DN A1999-21-6822-001
 TI The effect of germanium on the Co-SiGe thin-film reaction.
 AU Boyanov, B.I.; Goeller, P.T.; Sayers, D.E.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)
 SO Journal of Synchrotron Radiation (1 May 1999) vol.6, no.3, p.521-3. 8 refs.
 Published by: Munksgaard International Booksellers and Publishers for Int. Union Crystallogr
 CODEN: JSYRES ISSN: 0909-0495
 SICI: 0909-0495(19990501)6:3L.521:EGST;1-G
 Conference: Tenth International Conference on X-Ray Absorption Fine Structure. XAFS X. Chicago, IL, USA, 10-14 Aug 1998
 DT Conference Article; Journal
 TC Experimental
 CY Denmark
 LA English

L4 ANSWER 38 OF 155 INSPEC (C) 2005 IEE on STN

FULL **TEX**

AN 1999:6355468 INSPEC DN A1999-20-6822-023; B1999-10-2550F-042
 TI Thermal stability of cobalt silicide stripes on Si (001).
 AU Alberti, A. (Dipt. di Fisica, Catania Univ., Italy); La Via, F.; Raineri, V.; Rimini, E.
 SO Journal of Applied Physics (15 Sept. 1999) vol.86, no.6, p.3089-95. 20 refs.
 Doc. No.: S0021-8979(99)04918-X
 Published by: AIP
 Price: CCCC 0021-8979/99/86(6)/3089(7) /\$15.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(19990915)86:6L.3089:TSCS;1-1
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 39 OF 155 INSPEC (C) 2005 IEE on STN

FULL **TEX**

AN 1999:6326626 INSPEC DN A1999-19-6822-005
 TI Reaction and thermal stability of cobalt disilicide on polysilicon resulting from a Si/Ti/Co multilayer system.
 AU Alberti, A. (Dipt. di Fisica, Catania Univ., Italy); La Via, F.; Rimini, F.
 SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (July 1999) vol.17, no.4, p.1448-55. 20 refs.
 Doc. No.: S0734-211X(99)01404-3
 Published by: AIP for American Vacuum Soc
 Price: CCCC 0734-211X/99/17(4)/1448(8) /\$15.00
 CODEN: JVTD9 ISSN: 0734-211X
 SICI: 0734-211X(199907)17:4L.1448:RTSC;1-G
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 40 OF 155 INSPEC (C) 2005 IEE on STN

AN 1999:6309004 INSPEC DN A1999-17-6170T-018; B1999-09-2550B-018
 TI Initial stages of **cobalt-disilicide** formation in mesotaxy.
 AU Carlow, G.R.; Zinke-Allmang, M. (Dept. of Phys. & Astron., Univ. of Western Ontario, London, Ont., Canada)
 SO Canadian Journal of Chemistry (Nov. 1998) vol.76, no.11, p.1737-45. 29 refs.
 Published by: Natl. Res. Council Canada
 Price: CCCC 0008-4042/98/\$7.00
 CODEN: CJCHAG ISSN: 0008-4042
 SICI: 0008-4042(199811)76:11L.1737:ISCD;1-6
 DT Journal
 TC Experimental
 CY Canada
 LA English

L4 ANSWER 41 OF 155 INSPEC (C) 2005 IEE on STN

AN 1999:6226422 INSPEC DN B1999-05-2550N-020
 TI Nanopatterning of thin **cobalt disilicide** layers by local oxidation.
 AU Klinkhammer, F.; Kappius, L.; Antons, A.; Dolle, M.; Trinkaus, H.; Mesters, S.; Bochem, H.-P.; Mantl, S. (Forschungszentrum Julich GmbH, Germany); Heinig, K.-H.
 SO Advanced Interconnects and Contact Materials and Processes for Future Integrated Circuits. Symposium
 Editor(s): Murarka, S.P.; Eizenberg, M.; Fraser, D.B.; Madar, R.; Tung, R. Warrendale, PA, USA: Mater. Res. Soc, 1998. p.163 of xvl+560 pp. 0 refs.
 Conference: San Francisco, CA, USA, 13-16 April 1998
 ISBN: 1-55899-420-3
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 42 OF 155 INSPEC (C) 2005 IEE on STN

AN 1999:6220409 INSPEC DN B1999-05-2550F-087
 TI Growth, patterning and microelectronic applications of epitaxial **cobalt disilicide**.
 AU Mantl, S.; Kappius, L.; Antons, A.; Loken, M.; Klinkhammer, F.; Dolle, M.; Zhao, Q.T.; Mesters, S.; Buchal, C.; Bay, H.L. (Inst. fur Schicht- und Ionentechnik, Forschungszentrum Julich GmbH, Germany); Kabius, B.; Trinkaus, H.; Heinig, K.H.
 SO Advanced Interconnects and Contact Materials and Processes for Future Integrated Circuits. Symposium
 Editor(s): Murarka, S.P.; Eizenberg, M.; Fraser, D.B.; Madar, R.; Tung, R. Warrendale, PA, USA: Mater. Res. Soc, 1998. p.145-55 of xvl+560 pp. 24 refs.
 Conference: San Francisco, CA, USA, 13-16 April 1998
 ISBN: 1-55899-420-3
 DT Conference Article
 TC Application; Practical; Experimental
 CY United States
 LA English

L4 ANSWER 43 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text Version

AN 1999:6211931 INSPEC DN A1999-10-6180J-042; B1999-05-2550B-112
 TI Dwell-time effects in focused ion beam synthesis of cobalt disilicide: reflectivity measurements.
 AU Hausmann, S.; Bischoff, L.; Voelskow, M.; Teichert, J.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf e.V., Dresden, Germany); Fuhrmann, H.
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (Jan. 1999) vol.148, no.1-4, p.610-14. 12 refs.
 Doc. No.: S0168-583X(98)00786-1
 Published by: Elsevier
 Price: CCCC 0168-583X/98/\$19.00
 CODEN: NIMBEU ISSN: 0168-583X
 SICI: 0168-583X(199901)148:1/4L.610:DTEF;1-O
 Conference: Eleventh International Conference on Ion Beam Modification of Materials. Amsterdam, Netherlands, 31 Aug-4 Sept 1998
 Sponsor(s): Found. Fundamental Res. Matter; Utrecht Univ.; Philips Res.; KLM Royal Dutch Airlines; et al
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 44 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text Version

AN 1999:6211799 INSPEC DN A1999-10-6170T-020; B1999-05-2550B-046
 TI Dwell-time dependence of the defect accumulation in focused ion beam synthesis of CoSi₂.
 AU Bischoff, L.; Hausmann, S.; Voelskow, M.; Teichert, J. (Inst. fuer Ionenstrahlphysik und Materialforschung, Forschungszentrum Rossendorf e.V., Dresden, Germany)
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (1 Jan. 1999) vol.147, no.1-4, p.327-31. 11 refs.
 Doc. No.: S0168-583X(98)00533-3
 Published by: Elsevier
 Price: CCCC 0168-583X/98/\$19.00
 CODEN: NIMBEU ISSN: 0168-583X
 SICI: 0168-583X(19990101)147:1/4L.327:DTDD;1-G
 Conference: E-MRS 1998 Spring Meeting Symposium J on Ion Implantation into Semiconductors Oxides and Ceramics. Strasbourg, France, 16-19 June 1998
 Sponsor(s): Council of Eur.; Comm. Eur. Communities
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

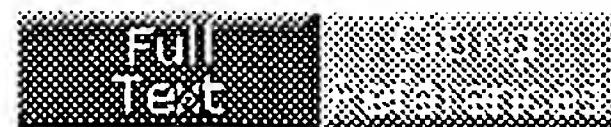
L4 ANSWER 45 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Version

AN 1999:6141356 INSPEC DN A1999-04-6855-077
 TI Thin film microstructures produced by nucleation and growth-to-impingement.
 AU Frost, H.J. (Thayer Sch. of Eng., Dartmouth Coll., Hanover, NH, USA); Thompson, C.V.
 SO Boundaries and Interfaces in Materials: David A. Smith Symposium. Proceedings of the Memorial Symposium Held at the 1997 TMS Fall Meeting

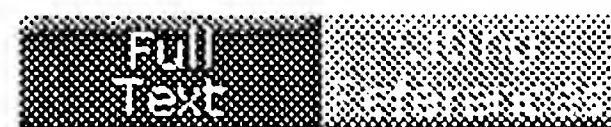
Editor(s): Pond, R.C.; Clark, W.A.T.; King, A.H.; Williams, D.B.
 Warrendale, PA, USA: TMS, 1998. p.237-47 of xxxii+348 pp. 86 refs.
 Conference: Indianapolis, IN, USA, 15-18 Sept 1997
 Sponsor(s): TMS
 ISBN: 0-87339-404-6
 DT Conference Article
 TC Theoretical
 CY United States
 LA English

L4 ANSWER 46 OF 155 INSPEC (C) 2005 IEE on STN

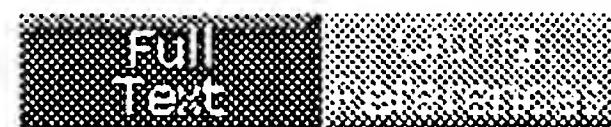
AN 1998:6095263 INSPEC DN A9901-6180M-002
 TI RBS and channeling analysis of **cobalt disilicide** layers produced by focused ion beam implantation.
 AU Teichert, J.; Voelskow, M.; Bischoff, L.; Hausmann, S. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf, Dresden, Germany)
 SO Vacuum (Oct. 1998) vol.51, no.2, p.261-6. 11 refs.
 Doc. No.: S0042-207X(98)00171-7
 Published by: Elsevier
 Price: CCCC 0042-207X/98/\$19.00+.00
 CODEN: VACUAV ISSN: 0042-207X
 SICI: 0042-207X(199810)51:2L.261:CACD;1-P
 Conference: Vacuum, Electron and Ion Technolgies. 10th International Summer School VEIT'97. Varna, Bulgaria, 22-26 Sept 1997
 DT Conference Article; Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 47 OF 155 INSPEC (C) 2005 IEE on STN

AN 1998:6048781 INSPEC DN A9822-8115I-008
 TI **Cobalt disilicide**-induced crystallization of amorphous silicon under XeCl excimer laser irradiation.
 AU Luby, S.; Majkova, E.; Jergel, M. (Inst. of Phys., Slovak Acad. of Sci., Bratislava, Slovakia); D'Anna, E.; Luches, A.; Martino, M.; Mengucci, P.; Majni, G.; Dobrocka, E.
 SO Laser Physics (Jan.-Feb. 1998) vol.8, no.1, p.259-64. 24 refs.
 Published by: MAIK Nauka/Interperiodica Publishing
 CODEN: LAPHEJ ISSN: 1054-660X
 SICI: 1054-660X(199801/02)8:1L.259:CDIC;1-M
 Conference: Sixth International Workshop on Laser Physics (LPHYS'97). Prague, Czech Republic, 4-8 Aug 1997
 DT Conference Article; Journal
 TC Experimental
 CY Russian Federation
 LA English

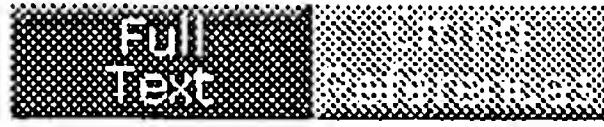
L4 ANSWER 48 OF 155 INSPEC (C) 2005 IEE on STN

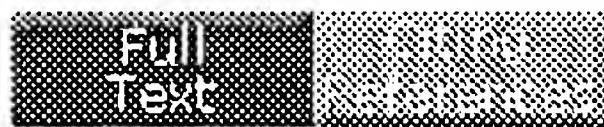
AN 1998:6012198 INSPEC DN A9820-6170T-003; B9810-2550B-019
 TI Ion beam synthesis of **cobalt disilicide** using focused ion beam implantation.
 AU Teichert, J.; Bischoff, L.; Hausmann, S. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf e.V., Dresden, Germany)

SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (July-Aug. 1998) vol.16, no.4, p.2574-7. 13 refs.
 Doc. No.: S0734-211X(98)04404-7
 Published by: AIP for American Vacuum Soc
 Price: CCCC 0734-211X/98/16(4)/2574(4)/\$15.00
 CODEN: JVTBD9 ISSN: 0734-211X
 SICI: 0734-211X(199807/08)16:4L.2574:BSCD;1-L
 Conference: Japan/US Workshop on Formation of Ion Nanobeams. Osaka, Japan,
 16-20 Nov 1997
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 49 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN


 AN 1998:5997835 INSPEC DN A9818-6855-172
 TI Co-deposition of cobalt disilicide on silicon-germanium thin films.
 AU Goeller, P.T.; Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)
 SO Thin Solid Films (18 May 1998) vol.320, no.2, p.206-10. 12 refs.
 Doc. No.: S0040-6090(97)00941-3
 Published by: Elsevier
 Price: CCCC 0040-6090/98/\$19.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(19980518)320:2L.206:DCDS;1-7
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 50 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

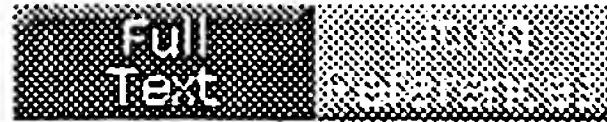

 AN 1998:5963100 INSPEC DN A9816-6822-003
 TI Structural analysis of buried conducting CoSi₂ layers formed in Si by high-dose Co ion implantation.
 AU Galayev, A.A. (Inst. of Chem. Problems in Microelectron., Moscow, Russia); Parkhomenko, Yu.N.; Chtcherbatchev, K.D.; Podgorny, D.A.; Belogorohov, A.I.; Dieguez, A.; Romano-Rodriguez, A.; Perez-Rodriguez, A.; Morante, J.R.
 SO Journal of Crystal Growth (May 1998) vol.187, no.3-4, p.435-43. 11 refs.
 Doc. No.: S0022-0248(97)00600-3
 Published by: Elsevier
 Price: CCCC 0022-0248/98/\$19.00
 CODEN: JCRGAE ISSN: 0022-0248
 SICI: 0022-0248(199805)187:3/4L.435:SABC;1-P
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 51 OF 155 INSPEC (C) 2005 IEE on STN

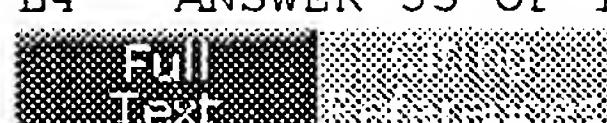

 AN 1998:5946626 INSPEC DN A9815-8115H-001; B9808-0520F-002
 TI Growth of carbon nanotubes on cobalt disilicide precipitates by chemical vapor deposition.
 AU Mao, J.M.; Sun, L.F.; Qian, L.X.; Pan, Z.W.; Chang, B.H.; Zhou, W.Y.;

Wang, G.; Xie, S.S. (Inst. of Phys., Acad. Sinica, Beijing, China)
 SO Applied Physics Letters (22 June 1998) vol.72, no.25, p.3297-9. 12 refs.
 Doc. No.: S0003-6951(98)03625-0
 Published by: AIP
 Price: CCCC 0003-6951/98/72(25)/3297(3)/\$15.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(19980622)72:25L.3297:GCNC;1-7
 DT Journal
 TC Experimental
 CY United States
 LA English

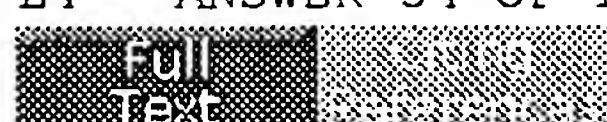
L4 ANSWER 52 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1998:5927847 INSPEC DN A9813-6170T-006; B9807-2550B-010
 TI Dose rate effects in focused ion beam synthesis of **cobalt disilicide**.
 AU Hausmann, S.; Bischoff, L.; Teichert, J.; Voelskow, M.; Grambole, D.; Herrmann, F.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf, Germany)
 SO Applied Physics Letters (25 May 1998) vol.72, no.21, p.2719-21. 16 refs.
 Doc. No.: S0003-6951(98)03421-4
 Published by: AIP
 Price: CCCC 0003-6951/98/72(21)/2719(3)/\$15.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(19980525)72:21L.2719:DREF;1-J
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 53 OF 155 INSPEC (C) 2005 IEE on STN

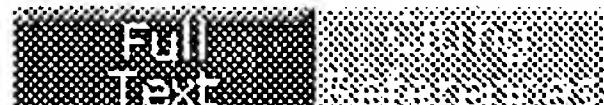

 AN 1998:5908786 INSPEC DN B9806-2550F-046
 TI Investigation of dwell-time effects on the **cobalt disilicide** formation using focused ion beam implantation.
 AU Hausmann, S.; Bischoff, L.; Teichert, J.; Grambole, D.; Herrmann, F.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf, Dresden, Germany)
 SO Microelectronic Engineering (March 1998) vol.41-42, p.233-6. 14 refs.
 Doc. No.: S0167-9317(98)00053-7
 Published by: Elsevier
 Price: CCCC 0167-9317/98/\$19.00
 CODEN: MIENEF ISSN: 0167-9317
 SICI: 0167-9317(199803)41/42L.233:IDTE;1-#
 Conference: Micro- and Nano- Engineering 97. MNE International Conference on Micro- and Nanofabrication. Athens, Greece, 15-18 Sept 1997
 DT Conference Article; Journal
 TC Practical; Experimental
 CY Netherlands
 LA English

L4 ANSWER 54 OF 155 INSPEC (C) 2005 IEE on STN

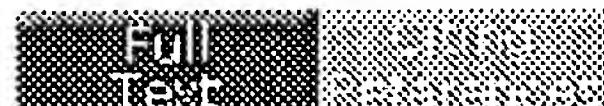

 AN 1998:5908152 INSPEC DN A9812-6855-007
 TI Studies of phase formation in CoSi₂ buried layers fabricated using ion implantation.
 AU Galaev, A.A.; Parkhomenko, Yu.N.; Podgornyi, D.A.; Shcherbachev, K.D.

(Inst. of Steel & Alloys, Moscow, Russia)
 SO Crystallography Reports (March-April 1998) vol.43, no.2, p.311-16. 8 refs.
 Published by: MAIK Nauka/Interperiodica Publishing
 Price: CCCC 1063-7745/98/4302-0311\$15.00
 CODEN: CYSTE3 ISSN: 1063-7745
 SICI (Trl): 1063-7745(199803/04)43:2L.311:SPFC;1-X
 Translation of: Kristallografiya (March-April 1998) vol.43, no.2,
 p.345-50. 8 refs.
 CODEN: KRISAJ ISSN: 0023-4761
 SICI: 0023-4761(199803/04)43:2L.345;1-J
 DT Journal; Translation Abstracted
 TC Practical; Experimental
 CY Russian Federation; Russian Federation
 LA English

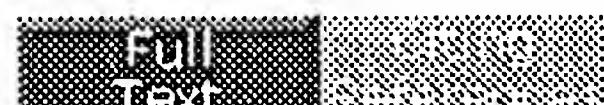
L4 ANSWER 55 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1998:5855819 INSPEC DN A9808-6855-096; B9804-2530D-016
 TI Thin films of CoSi₂ co-deposited onto Si_{1-x}Gex alloys.
 AU Goeller, P.T. (Dept. of Mater. Sci. & Eng., North Carolina State Univ.,
 Raleigh, NC, USA); Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J.
 SO Structure and Evolution of Surfaces. Symposium
 Editor(s): Cammarata, R.C.; Chason, E.H.; Einstein, T.L.; Williams, E.D.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.487-92 of xii+509 pp. 23
 refs.
 Conference: Boston, MA, USA, 2-5 Dec 1996
 ISBN: 1-55899-344-4
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 56 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1998:5855768 INSPEC DN B9804-2550A-007
 TI Thermal stability of cobalt and nickel silicides in amorphous and
 crystalline silicon.
 AU Poon, M.C. (Dept. of Electr. & Electron. Eng., Hong Kong Univ. of Sci. &
 Technol., Hong Kong); Deng, F.; Wong, H.; Wong, M.; Sin, J.K.O.; Lan,
 S.S.; Ho, C.H.; Han, P.G.
 SO Proceedings. 1997 IEEE Hong Kong Electron Devices Meeting (Cat.
 No.97TH8260)
 New York, NY, USA: IEEE, 1997. p.65-8 of v+160 pp. 7 refs.
 Conference: Hong Kong, 30 Aug 1997
 Sponsor(s): IEEE Electron. Devices Soc.; Dept. Electron. Eng. City Univ.
 Hong Kong
 ISBN: 0-7803-3802-2
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 57 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1998:5825115 INSPEC DN B9803-2550F-058
 TI Submicrometer patterning of cobaltdisilicide layers by local oxidation.
 AU Klinkhammer, F.; Dolle, M.; Kappius, L.; Mantl, S. (Inst. fur Schicht- und

SO Ionentechnik, Forschungszentrum Julich GmbH, Germany)
 Microelectronic Engineering (Nov. 1997) vol.37-38, p.515-21. 8 refs.
 Doc. No.: S0167-9317(97)00154-8
 Published by: Elsevier
 Price: CCCC 0167-9317/97/\$17.00
 CODEN: MIENEF ISSN: 0167-9317
 SICI: 0167-9317(199711)37/38L.515:SPCL;1-5
 Conference: Second European Workshop on Materials for Advanced
 Metallization. MAM'97. Villard de Lans, France, 16-19 March 1997
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist.
 Educ. Nat. Enseignement Superieur
 DT Conference Article; Journal
 TC Practical; Experimental
 CY Netherlands
 LA English

L4 ANSWER 58 OF 155 INSPEC (C) 2005 IEE on STN

AN 1998:5825112 INSPEC DN B9803-2550F-055
 TI Arsenic solubility in single crystalline **cobalt disilicide**.
 AU Mangelinck, D.; Cardenas, J.; Svensson, B.G. (Solid State Electron., R.
 Inst. of Technol., Stockholm, Sweden)
 SO Microelectronic Engineering (Nov. 1997) vol.37-38, p.467-73. 20 refs.
 Doc. No.: S0167-9317(97)00148-2
 Published by: Elsevier
 Price: CCCC 0167-9317/97/\$17.00
 CODEN: MIENEF ISSN: 0167-9317
 SICI: 0167-9317(199711)37/38L.467:ASSC;1-9
 Conference: Second European Workshop on Materials for Advanced
 Metallization. MAM'97. Villard de Lans, France, 16-19 March 1997
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist.
 Educ. Nat. Enseignement Superieur
 DT Conference Article; Journal
 TC Practical; Experimental
 CY Netherlands
 LA English

L4 ANSWER 59 OF 155 INSPEC (C) 2005 IEE on STN

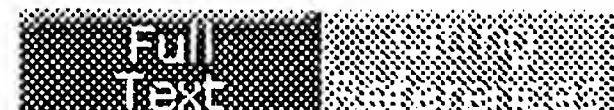
AN 1998:5815922 INSPEC DN A9805-6855-048; B9803-0510D-037
 TI Thin films of CoSi₂ co-deposited onto Si_{1-x}Gex alloys.
 AU Goeller, P.T. (Dept. of Mater. Sci., North Carolina State Univ., Raleigh,
 NC, USA); Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J.
 SO Control of Semiconductor Surfaces and Interfaces. Symposium
 Editor(s): Prokes, S.M.; Glembotzki, O.J.; Brierley, S.K.; Gibson, J.M.;
 Woodall, J.M.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.365-70 of xiii+505 pp. 23
 refs.
 Conference: Boston, MA, USA, 2-5 Dec 1996
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 60 OF 155 INSPEC (C) 2005 IEE on STN

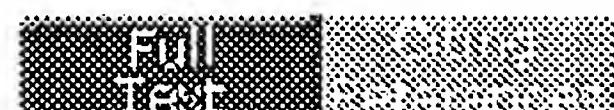
AN 1998:5810079 INSPEC DN A9805-7840-001

TI Color in Pettifor's structure maps: intermetallic compounds for a new use.
 AU Steinemann, S.G.; Anongba, O.N.B. (Inst. de Phys. Exp., Lausanne Univ., Switzerland); Podloucky, R.
 SO Journal of Phase Equilibria (Dec. 1997) vol.18, no.6, p.655-62. 48 refs.
 Published by: ASM Int
 Price: CCCC 1054-9714/97/\$4.00
 CODEN: JPEQE6 ISSN: 1054-9714
 SICI: 1054-9714(199712)18:6L.655:CPSM;1-D
 Conference: Hume-Rothery Award Symposium held at the TMS Annual Meeting.
 Las Vegas, NV, USA, 12-16 Feb 1995
 DT Conference Article; Journal
 TC General Review; Theoretical; Experimental
 CY United States
 LA English

L4 ANSWER 61 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1998:5787851 INSPEC DN A9803-7335-009
 TI Observation of quantum interference effects in submicron CoSi₂ wires in Si(100).
 AU Lenssen, D.; Manti, S. (Inst. fur Schicht- und Ionentechnik, Julich, Germany)
 SO Applied Physics Letters (15 Dec. 1997) vol.71, no.24, p.3540-2. 13 refs.
 Doc. No.: S0003-6951(97)03150-1
 Published by: AIP
 Price: CCCC 0003-6951/97/71(24)/3540/3/\$10.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(19971215)71:24L.3540:OQIE;1-9
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 62 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1997:5780387 INSPEC DN A9802-6460-008; B9801-2550F-099
 TI Local nucleation and lateral crystallisation of the silicide phases in CoSi₂ buffer layer of YBCO/CoSi₂/Si structure.
 AU Belousov, I.; Rudenko, E. (Inst. of Mater. Phys., Acad. of Sci., Kiev, Ukraine); Linzen, S.; Seidel, P.
 SO European Workshop. Materials for Advanced Metallization. MAM'97 Abstracts Booklet (IEEE Cat. No.97TH8287)
 Paris, France: Soc. Francaise du Vide, 1997. p.185-8 of 221 pp. 6 refs.
 Conference: Villard de Lans, France, 16-19 March 1997
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist. Educ. Nat. Enseignement Superieur
 DT Conference Article
 TC Application; Experimental
 CY France
 LA English

L4 ANSWER 63 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1997:5780375 INSPEC DN B9801-2550F-090
 TI Arsenic solubility in single crystalline cobalt disilicide.
 AU Mangelinck, D.; Cardenas, J.; Svensson, B.G. (Solid State Electron., R. Inst. of Technol., Stockholm, Sweden)

SO European Workshop. Materials for Advanced Metallization. MAM'97 Abstracts Booklet (IEEE Cat. No.97TH8287)
 Paris, France: Soc. Francaise du Vide, 1997. p.120-1 of 221 pp. 5 refs.
 Conference: Villard de Lans, France, 16-19 March 1997
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist.
 Educ. Nat. Enseignement Superieur
 DT Conference Article
 TC Practical; Experimental
 CY France
 LA English

L4 ANSWER 64 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5744591 INSPEC DN A9724-7340N-003; B9712-2550F-028
 TI Quantum transport in ion beam synthesized **cobalt disilicide** wires.
 AU Lenssen, D.; Mesters, S.; Mantl, S. (Inst. for Thin Film & Ion Technol., Forschungszentrum Julich GmbH, Germany)
 SO Materials Modification and Synthesis by Ion Beam Processing. Symposium
 Editor(s): Alexander, D.E.; Cheung, N.W.; Park, B.; Skorupa, W.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.295-300 of xix+727 pp. 9 refs.
 Conference: Boston, MA, USA, 2-5 Dec 1996
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 65 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text

AN 1997:5681147 INSPEC DN A9719-2940-055; B9710-7420-026
 TI Fabrication of an integrated Delta E-E-silicon detector by wafer bonding using **cobalt disilicide**.
 AU Thungstroem, G. (Dept. of Inf. Technol., Mid-Sweden Univ., Sundsvall, Sweden); van Veldhuizen, E.J.; Westerberg, L.; Norlin, L.-O.; Petersson, C.S.
 SO Nuclear Instruments & Methods in Physics Research, Section A (Accelerators, Spectrometers, Detectors and Associated Equipment) (1 June 1997) vol.391, no.2, p.315-28. 13 refs.
 Doc. No.: S0168-9002(97)00408-7
 Published by: Elsevier
 Price: CCCC 0168-9002/97/\$17.00
 CODEN: NIMAER ISSN: 0168-9002
 SICI: 0168-9002(19970601)391:2L.315:FISD;1-B
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 66 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5664390 INSPEC DN B9709-2550F-042
 TI Silicidation strategy of sub-0.1 μ m junctions for deep submicron devices.
 AU Jiunn-Yann Tsai; Osburn, C.M. (Dept. of Electr. & Comput. Eng., North Carolina State Univ., Raleigh, NC, USA); Hsia, S.L.
 SO Silicide Thin Films - Fabrication, Properties, and Applications. Symposium
 Editor(s): Tung, R.T.; Maex, K.; Pellegrini, P.W.; Allen, L.H.

Pittsburgh, PA, USA: Mater. Res. Soc, 1996. p.245-50 of xv+648 pp. 19 refs.

Conference: Boston, MA, USA, 27-30 Nov 1995

DT Conference Article

TC Practical

CY United States

LA English

L4 ANSWER 67 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5657371 INSPEC DN A9718-8115G-020; B9709-0510D-130
 TI Epitaxial films of **cobalt disilicide** (100) evaporated onto Si (100) from a mixed source.
 AU Goeller, P.T.; Wang, Z.; Sayers, D.E.; Glass, J.T.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)
 SO Silicide Thin Films - Fabrication, Properties, and Applications. Symposium Editor(s): Tung, R.T.; Maex, K.; Pellegrini, P.W.; Allen, L.H. Pittsburgh, PA, USA: Mater. Res. Soc, 1996. p.511-16 of xv+648 pp. 12 refs.
 Conference: Boston, MA, USA, 27-30 Nov 1995
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 68 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5534859 INSPEC DN A9709-6822-017; B9705-0510D-086
 TI Co silicide formation on SiGeC/Si and SiGe/Si layers.
 AU Donaton, R.A.; Maex, K. (IMEC, Leuven, Belgium); Vantomme, A.; Langouche, G.; Morciaux, Y.; St. Amour, A.; Sturm, J.C.
 SO Applied Physics Letters (10 March 1997) vol.70, no.10, p.1266-8. 13 refs. Doc. No.: S0003-6951(97)00610-4
 Published by: AIP
 Price: CCCC 0003-6951/97/70(10)/1266/3/\$10.00
 CODEN: APPLAB ISSN: 0003-6951
 SICI: 0003-6951(19970310)70:10L.1266:SFSS;1-J
 DT Journal
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 69 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5530238 INSPEC DN A9709-7475-002; B9705-3220-005
 TI **Cobalt disilicide** buffer layer for YBCO film on silicon.
 AU Belousov, I.; Rudenko, E. (Inst. of Phys. of Metals, Acad. of Sci., Kiev, Ukraine); Linzen, S.; Seidel, P.
 SO Journal of Low Temperature Physics (Feb. 1997) vol.106, no.3-4, p.433-8. 9 refs.
 Published by: Plenum
 Price: CCCC 0022-2291/97/0200-0433\$12.50/0
 CODEN: JLTPAC ISSN: 0022-2291
 SICI: 0022-2291(199702)106:3/4L.433:CDBL;1-#
 Conference: Weak Superconductivity Symposium. Smolenice Castle, Slovakia, 4-7 Aug 1996
 DT Conference Article; Journal

TC Experimental
 CY United States
 LA English

L4 ANSWER 70 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text

AN 1996:5459760 INSPEC DN A9703-8115N-003
 TI Diffusing species and growth interfaces during **cobalt disilicide** formation.
 AU Comrie, C.M. (Cape Town Univ., Rondebosch, South Africa)
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (Sept. 1996) vol.118, no.1-4, p.119-22. 12 refs.
 Published by: Elsevier
 Price: CCCC 0168-583X/96/\$15.00
 CODEN: NIMBEU ISSN: 0168-583X
 SICI: 0168-583X(199609)118:1/4L.119:DSGI;1-8
 Conference: Ion Beam Analysis. Twelfth International Conference. Tempe, AZ, USA, 22-26 May 1995
 Sponsor(s): Arizona State Univ.; Bohmische Soc.; et al
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 71 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1996:5382948 INSPEC DN A9621-6630J-002
 TI Solid solubility and diffusion of boron in single-crystalline **cobalt disilicide**.
 AU Zaring, C.; Pisch, A.; Cardenas, J. (R. Inst. of Technol., Stockholm, Sweden); Gas, P.; Svensson, B.G.
 SO Journal of Applied Physics (1 Sept. 1996) vol.80, no.5, p.2742-8. 35 refs.
 Doc. No.: S0021-8979(96)06117-8
 Published by: AIP
 Price: CCCC 0021-8979/96/80(5)/2742/7/\$10.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(19960901)80:5L.2742:SSDB;1-H
 DT Journal
 TC Experimental
 CY United States
 LA English

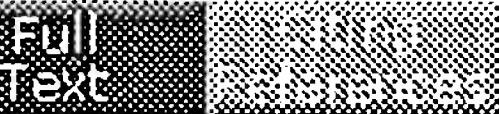
L4 ANSWER 72 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

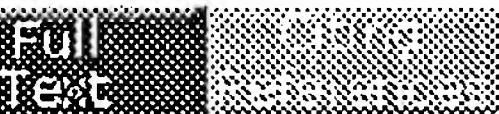
AN 1996:5340719 INSPEC DN B9609-2560H-008
 TI Self-aligned **cobalt disilicide**/silicon Schottky barrier diodes.
 AU Woods, N.J.; Hall, S. (Dept. of Electr. Eng. & Electron., Liverpool Univ., UK)
 SO ESSDERC '95. Proceedings of the 25th European Solid State Device Research Conference
 Editor(s): de Graaff, H.C.; van Kranenburg, H.
 Gif sur Yvette, France: Editions Frontieres, 1995. p.517-20 of xlv+847 pp.
 5 refs.
 Conference: The Hague, Netherlands, 25-27 Sept 1995
 Sponsor(s): Philips Semicond.; EU; ASM-Lithography; Appl. Mater.; GSM Nederland; ASM Int.; Novellus Syst.; Philips Machine Factories et al

ISBN: 2-86332-182-X
 DT Conference Article
 TC Practical; Theoretical; Experimental
 CY France
 LA English

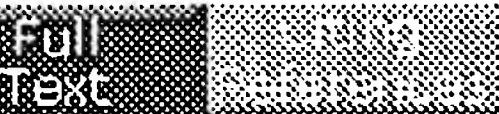
L4 ANSWER 73 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1996:5320634 INSPEC DN A9616-7340N-006; B9608-2530D-020
 TI Self-aligned cobalt disilicide/silicon Schottky barrier contacts: fabrication, materials and electrical characterization.
 AU Woods, N.J.; Hall, S. (Dept. of Electr. Eng. & Electron., Liverpool Univ., UK)
 SO Semiconductor Science and Technology (July 1996) vol.11, no.7, p.1103-15. 21 refs.
 Published by: IOP Publishing
 Price: CCCC 0268-1242/96/071103+13\$19.50
 CODEN: SSTEET ISSN: 0268-1242
 SICI: 0268-1242(199607)11:7L.1103:SACD;1-E
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 74 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1996:5314473 INSPEC DN B9608-2575-069
 TI Cobalt disilicide interconnects for micromechanical devices.
 AU Teichert, J.; Bischoff, L.; Hesse, E.; Schneider, P.; Panknin, D. (Inst. of Ion Beam Phys., Res. Centre Rossendorf Inc., Dresden, Germany); Gessner, T.; Lobner, B.; Zichner, N.
 SO Journal of Micromechanics and Microengineering (June 1996) vol.6, no.2, p.272-8. 17 refs.
 Published by: IOP Publishing
 Price: CCCC 0960-1317/96/020272+07\$19.50
 CODEN: JMMIEZ ISSN: 0960-1317
 SICI: 0960-1317(199606)6:2L.272:CDIM;1-P
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 75 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1996:5301972 INSPEC DN A9615-7125R-001
 TI Electronic structure of a buried NiSi₂ or CoSi₂ layer in bulk Si.
 AU Schick, J.T. (Dept. of Phys., Villanova Univ., PA, USA); Bose, S.M.
 SO Physical Review B (Condensed Matter) (15 May 1996) vol.53, no.19, p.12609-12. 21 refs.
 Doc. No.: S0163-1829(96)09119-9
 Published by: APS through AIP
 Price: CCCC 0163-1829/96/53(19)/12609(4)\$10.00
 CODEN: PRBMDO ISSN: 0163-1829
 SICI: 0163-1829(19960515)53:19L.12609:ESBN;1-N
 DT Journal
 TC Experimental
 CY United States

LA English

L4 ANSWER 76 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1996:5183907 INSPEC DN A9605-8115I-011; B9603-0520F-061
 TI Study of WSi₂ and CoSi₂ thin films deposited by laser ablation.
 AU Glebovsky, V.G.; Ermolov, S.N.; Oganyan, R.A.; Stinov, E.D. (Inst. of Solid State Phys., Acad. of Sci., Chernogolovka, Russia)
 SO Beam-Solid Interactions for Materials Synthesis and Characterization. Symposium
 Editor(s): Jacobson, D.C.; Luzzi, D.E.; Heinz, T.F.; Iwaki, M.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1995. p.659-64 of xv+746 pp. 4 refs.
 Conference: Boston, MA, USA, 28 Nov-2 Dec 1994
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 77 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1996:5173528 INSPEC DN A9605-6822-004; B9603-2550F-023
 TI Dominant diffusing species during cobalt silicide formation.
 AU Comrie, M.; Newman, R.T. (Cape Town Univ., Rondebosch, South Africa)
 SO Journal of Applied Physics (1 Jan. 1996) vol.79, no.1, p.153-6. 18 refs.
 Published by: AIP
 Price: CCCC 0021-8979/96/79(1)/153/4/\$6.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(19960101)79:1L.153:DDSD;1-X
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 78 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:5135159 INSPEC DN A9602-6855-044
 TI Formation of CoSi₂ on strained Si_{0.8}Ge_{0.2} using a sacrificial Si layer.
 AU Donaton, R.A.; Kolodinski, S.; Caymax, M.; Roussel, P.; Bender, H.; Brijs, B.; Maex, K. (IMEC, Leuven, Belgium)
 SO Applied Surface Science (Oct. 1995) vol.91, p.77-81. 12 refs.
 Price: CCCC 0169-4332/95/\$09.50
 CODEN: ASUSEE ISSN: 0169-4332
 Conference: MAM 1995. First European Workshop on Materials for Advanced Metallization. Radebeul, Germany, 19-22 March 1995
 Sponsor(s): Bundesministerium fur Bildung, Wissenschaft, Forschung und Technol.; SIEMANS AG; Appl. Mater. GmbH; et al
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

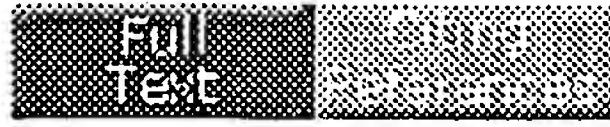
L4 ANSWER 79 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

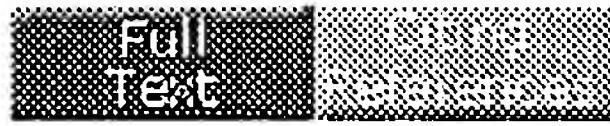
AN 1995:5111333 INSPEC DN A9524-7340N-012; B9512-2530D-033
 TI CoSi₂ ohmic contacts to n-type 6H-SiC.
 AU Lundberg, N.; Ostling, M. (Dept. of Electron., R. Inst. of Technol.,

Stockholm, Sweden)
 SO Solid-State Electronics (Dec. 1995) vol.38, no.12, p.2023-8. 30 refs.
 Price: CCCC 0038-1101/95/\$9.50+0.00
 CODEN: SSELAS5 ISSN: 0038-1101
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

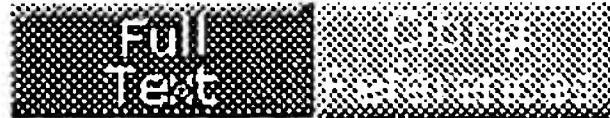
L4 ANSWER 80 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1995:5108958 INSPEC DN B9512-2560H-016
 TI One micrometre scale self-aligned **cobalt disilicide** Schottky barrier diodes.
 AU Woods, N.J.; Hall, S. (Dept. of Electr. Eng. & Electron., Liverpool Univ., UK)
 SO Electronics Letters (12 Oct. 1995) vol.31, no.21, p.1878-80. 4 refs.
 Price: CCCC 0013-5194/95/\$10.00
 CODEN: ELLEAK ISSN: 0013-5194
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 81 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1995:5092532 INSPEC DN A9523-7125P-002
 TI Anisotropy of electronic distribution in a **cobalt disilicide** single crystal.
 AU Bellin, C.; Loupias, G. (Lab. de Miner.-Cristallogr., Paris VI Univ., France); Manuel, A.A.; Jarlborg, T.; Sakurai, Y.; Tanaka, Y.; Shiotani, N.
 SO Solid State Communications (Nov. 1995) vol.96, no.8, p.563-7. 28 refs.
 Price: CCCC 0038-1098/95/\$9.50+.00
 CODEN: SSCOAA4 ISSN: 0038-1098
 DT Journal
 TC Theoretical; Experimental
 CY United States
 LA English

L4 ANSWER 82 OF 155 INSPEC (C) 2005 IEE on STN

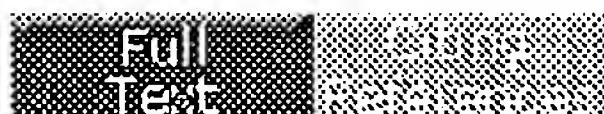

 AN 1995:5053984 INSPEC DN A9520-6822-020; B9511-0510D-018
 TI Layer reversal of Co/Zr bilayer and epitaxial growth of CoSi₂ layer on Si(001) substrate.
 AU Jeong Soo Byun; Jae Jeong Kim; Woo Shik Kim (ULSI Lab., LG Semicon Co. Ltd., Cheongju, South Korea); Hyeong Joon Kim
 SO Journal of the Electrochemical Society (Aug. 1995) vol.142, no.8, p.2805-12. 25 refs.
 Price: CCCC 0013-4651/95/\$5.00+0.00
 CODEN: JESOAN ISSN: 0013-4651
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 83 OF 155 INSPEC (C) 2005 IEE on STN



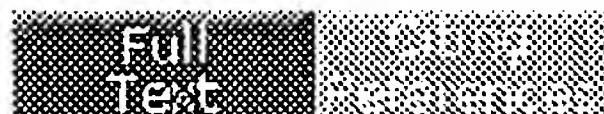
AN 1995:5051601 INSPEC DN A9520-6150C-004
 TI Analysis of crystal nucleation and growth in amorphous cobalt disilicide.
 AU Smith, D.A. (Stevens Inst. of Technol., Hoboken, NJ, USA); Evans, P.V.;
 Koppikar, S.R.
 SO Crystallization and Related Phenomena in Amorphous Materials. Symposium
 Editor(s): Libera, M.; Haynes, T.E.; Cebe, P.; Dickinson, J.E., Jr.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1994. p.271-82 of xv+755 pp. 9 refs.
 Conference: Boston, MA, USA, 29 Nov-2 Dec 1993
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 84 OF 155 INSPEC (C) 2005 IEE on STN



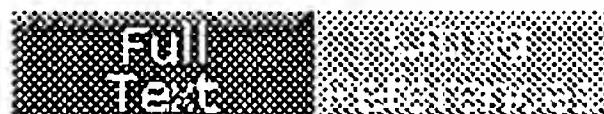
AN 1995:5047860 INSPEC DN A9520-7340N-002; B9510-2530D-023
 TI Low-temperature processing of shallow junctions using epitaxial and
 polycrystalline CoSi₂.
 AU Jones, E.C.; Cheung, N.W. (Dept. of Electr. Eng. & Comput. Sci.,
 California Univ., Berkeley, CA, USA); Fraser, D.B.
 SO Journal of Electronic Materials (July 1995) vol.24, no.7, p.863-73. 30
 refs.
 CODEN: JECMA5 ISSN: 0361-5235
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 85 OF 155 INSPEC (C) 2005 IEE on STN



AN 1995:5037385 INSPEC DN A9519-6855-043
 TI Entropic origin of the free energy barrier to nucleation of crystallites
 in amorphous CoSi₂ thin films.
 AU Shi, F.G. (Dept. of Chem. Eng., California Univ., Irvine, CA, USA); Tu,
 K.N.
 SO Physical Review Letters (29 May 1995) vol.74, no.22, p.4476-8. 12 refs.
 Price: CCCC 0031-9007/95/74(22)/4476(3)\$06.00
 CODEN: PRLTAO ISSN: 0031-9007
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 86 OF 155 INSPEC (C) 2005 IEE on STN



AN 1995:5024444 INSPEC DN A9518-8160B-007; B9510-2550E-006
 TI Etching of CoSi₂ in HF-based solutions.
 AU Donaton, R.A.; Lokere, K.; Verbeeck, R.; Maex, K. (IMEC, Leuven, Belgium)
 SO Applied Surface Science (July 1995) vol.89, no.3, p.221-7. 4 refs.
 Price: CCCC 0169-4332/95/\$09.50
 CODEN: ASUSEE ISSN: 0169-4332
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 87 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:4990703 INSPEC DN A9515-6848-004
 TI Diffuse X-ray scattering from thin films with defects.
 AU Bahr, D.; Press, W. (Inst. fur Experimentalphys., Kiel Univ., Germany);
 Jebasinski, R.; Mantl, S.
 SO Physical Review B (Condensed Matter) (1 May 1995) vol.51, no.18,
 p.12223-7. 23 refs.
 Price: CCCC 0163-1829/95/51(18)/12223(5)/*\$6.00
 CODEN: PRBMDO ISSN: 0163-1829
 DT Journal
 TC Theoretical
 CY United States
 LA English

L4 ANSWER 88 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:4940117 INSPEC DN A9510-7330-007; B9506-2530D-025
 TI Buried Schottky contacts in patterned cobalt silicide layers in silicon
 using wafer bonding.
 AU Thungstrom, G.; Frojdh, C.; Petersson, C.S. (Dept. of Solid State
 Electron., R. Inst. of Technol., Kista, Sweden)
 SO Advanced Metallization for Devices and Circuits - Science, Technology and
 Manufacturability Symposium
 Editor(s): Murarka, S.P.; Katz, A.; Tu, K.N.; Maex, K.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1994. p.475-80 of xiv+768 pp. 6
 refs.
 Conference: San Francisco, CA, USA, 4-8 April 1994
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 89 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1994:4837860 INSPEC DN A9502-7340N-008; B9501-2530D-017
 TI Cobalt disilicide (CoSi₂) Schottky contacts to 6H-SiC.
 AU Lundberg, N.; Ostling, M. (Dept. of Electron., R. Inst. of Technol.,
 Stockholm, Sweden)
 SO Physica Scripta Volume T (1994) vol.T54, p.273-7. 13 refs.
 CODEN: PHSTBO ISSN: 0281-1847
 Conference: 16th Nordic Semiconductor Meeting. Laugarvatn, Iceland, 12-15
 June 1994
 DT Conference Article; Journal
 TC Experimental
 CY Sweden
 LA English

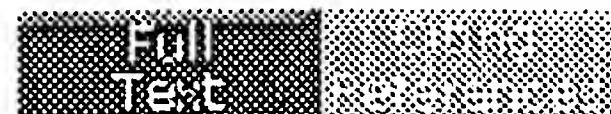
L4 ANSWER 90 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

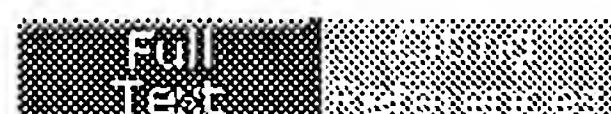
AN 1994:4837850 INSPEC DN B9501-2560J-021
 TI Process optimisation and characterisation of PBT structures.
 AU Hatzikonstantinidou, S.; Nilsson, H.-E.; Frojdh, C.; Petersson, C.S.
 (Dept. of Solid State Electron., R. Inst. of Technol., Stockholm, Sweden)
 SO Physica Scripta Volume T (1994) vol.T54, p.226-9. 10 refs.

CODEN: PHSTBO ISSN: 0281-1847
 Conference: 16th Nordic Semiconductor Meeting. Laugarvatn, Iceland, 12-15 June 1994
 DT Conference Article; Journal
 TC Practical; Experimental
 CY Sweden
 LA English

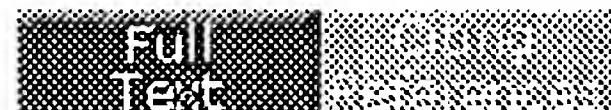
L4 ANSWER 91 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4837815 INSPEC DN B9501-2550-006
 TI Contacts to monocrystalline n- and p-type silicon by wafer bonding using cobalt disilicide.
 AU Thungstrom, G.; Frojdoh, C.; Svedberg, P.; Petersson, C.S. (Dept. of Solid State Electron., R. Inst. of Technol., Kista, Sweden)
 SO Physica Scripta Volume T (1994) vol.T54, p.77-80. 4 refs.
 CODEN: PHSTBO ISSN: 0281-1847
 Conference: 16th Nordic Semiconductor Meeting. Laugarvatn, Iceland, 12-15 June 1994
 DT Conference Article; Journal
 TC Practical
 CY Sweden
 LA English

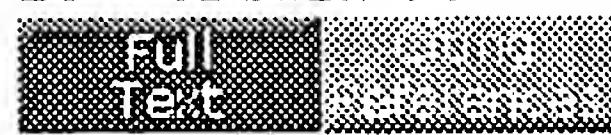
L4 ANSWER 92 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4810422 INSPEC DN A9424-6855-038
 TI Non-destructive characterization of the uniformity of thin cobalt disilicide films by Raman microprobe measurements.
 AU Perez-Rodriguez, A. (Dept. de Fisica Aplicada i Electron., Barcelona Univ., Spain); Roca, E.; Jawhari, T.; Morante, J.R.; Schreutelkamp, R.J.
 SO Thin Solid Films (15 Oct. 1994) vol.251, no.1, p.45-50. 11 refs.
 Price: CCCC 0040-6090/94/\$7.00
 CODEN: THSFAP ISSN: 0040-6090
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 93 OF 155 INSPEC (C) 2005 IEE on STN

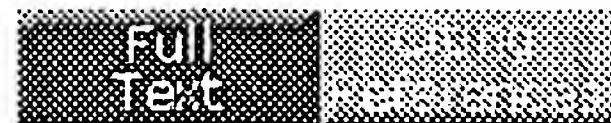

 AN 1994:4764029 INSPEC DN A9420-8115L-019
 TI Deposition of cobalt disilicide thin films by laser ablation of cast targets.
 AU Glebovsky, V.G.; Oganyan, R.A.; Ermolov, S.N. (Inst. of Solid State Phys., Chernogolovka, Russia); Kolosova, E.V.
 SO Thin Solid Films (15 Aug. 1994) vol.248, no.2, p.145-8. 9 refs.
 Price: CCCC 0040-6090/94/\$7.00
 CODEN: THSFAP ISSN: 0040-6090
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 94 OF 155 INSPEC (C) 2005 IEE on STN

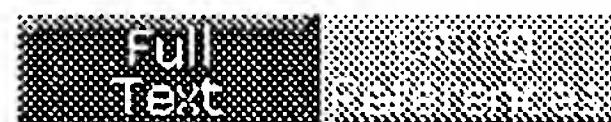


AN 1994:4762766 INSPEC DN A9420-8140N-065; C9410-7320-136
 TI Materials science from first-principles: CoSi₂ surfaces.
 AU Vogtenhuber, D.; Podloucky, R. (Inst. fur Phys. Chem., Wien Univ., Austria); Steinemann, S.G.
 SO Cray Channels (1994) vol.16, no.1, p.22-5. 6 refs.
 CODEN: CRCHE8
 DT Journal
 TC Practical
 CY United States
 LA English

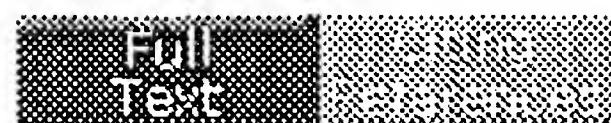
L4 ANSWER 95 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4749596 INSPEC DN A9419-6320D-013
 TI Ground-state properties of CoSi₂ determined by a total-energy pseudopotential method.
 AU Milman, V. (Div. of Solid State, Oak Ridge Nat. Lab., TN, USA); Lee, M.H.; Payne, M.C.
 SO Physical Review B (Condensed Matter) (15 June 1994) vol.49, no.23, p.16300-8. 42 refs.
 Price: CCCC 0163-1829/94/49(23)/16300(9)/\$6.00
 CODEN: PRBMDO ISSN: 0163-1829
 DT Journal
 TC Theoretical
 CY United States
 LA English

L4 ANSWER 96 OF 155 INSPEC (C) 2005 IEE on STN

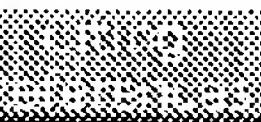

 AN 1994:4735635 INSPEC DN B9409-2560H-031
 TI Mixed Schottky/p-n junction behavior in diodes produced by outdiffusion from polycrystalline cobalt disilicide.
 AU Foyt, D. (IBM Corp., Essex Junction, VT, USA); Hanafi, H.; Agnello, P.; Ho, H.
 SO International Electron Devices Meeting 1992. Technical Digest (Cat. No.92CH3211-0)
 New York, NY, USA: IEEE, 1992. p.841-4 of 1022 pp. 10 refs.
 Conference: San Francisco, CA, USA, 13-16 Dec 1992
 Sponsor(s): Electron Devices Soc. IEEE
 Price: CCCC 0 7803 0817 4/92/\$3.00
 ISBN: 0-7803-0817-4
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 97 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4723027 INSPEC DN A9418-7865-009
 TI Optical Properties of buried cobalt disilicide layers in silicon.
 AU Lu, F.; Perry, C.H. (Dept. of Phys., Northeastern Univ., Boston, MA, USA); Namavar, F.
 SO Journal of Applied Physics (1 June 1994) vol.75, no.11, p.7465-9. 11 refs.
 Price: CCCC 0021-8979/94/75(11)/7465/5/\$6.00
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental

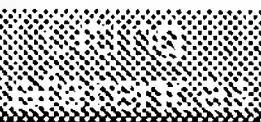
CY United States
 LA English

L4 ANSWER 98 OF 155 INSPEC (C) 2005 IEE on STN

AN 1994:4710320 INSPEC DN A9416-6170J-006
 TI Imaging misfit dislocations in epitaxial CoSi₂/Si(111) layers using quantum size microscopy.
 AU Kubby, J.A.; Greene, W.J. (Xerox Webster Res. Center, NY, USA)
 SO Surface Science (20 May 1994) vol.311, no.3, p.L695-702. 27 refs.
 Price: CCCC 0039-6028/94/\$07.00
 CODEN: SUSCAS ISSN: 0039-6028
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 99 OF 155 INSPEC (C) 2005 IEE on STN

AN 1994:4665371 INSPEC DN B9406-4250-015
 TI Cobalt disilicide intercell ohmic contacts for multijunction photovoltaic energy converters.
 AU Kalkhoran, N.M.; Maruska, H.P.; Namavar, F. (Spire Corp., Bedford, MA, USA)
 SO Applied Physics Letters (11 April 1994) vol.64, no.15, p.1980-2. 16 refs.
 Price: CCCC 0003-6951/94/64(15)/1980/3/\$6.00
 CODEN: APPLAB ISSN: 0003-6951
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 100 OF 155 INSPEC (C) 2005 IEE on STN

AN 1994:4652798 INSPEC DN A9411-6855-040
 TI Non-destructive thickness determination of thin cobalt and cobalt disilicide layers on silicon substrates.
 AU Roca, E. (Fac. de Fisica, Barcelona Univ., Spain); Vanhellemont, J.; Schreutelkamp, R.J.; Vermeiren, J.
 SO Thin Solid Films (15 March 1994) vol.240, no.1-2, p.110-13. 6 refs.
 Price: CCCC 0040-6090/94/\$7.00
 CODEN: THSFAP ISSN: 0040-6090
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

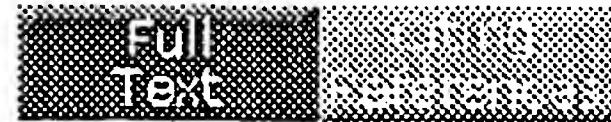
L4 ANSWER 101 OF 155 INSPEC (C) 2005 IEE on STN

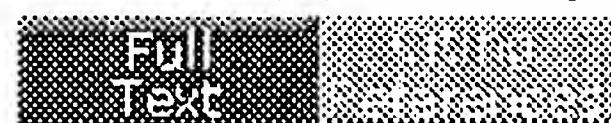
AN 1994:4649855 INSPEC DN A9411-6630J-001; B9406-2550B-005
 TI Solid source diffusion from agglomerating silicide sources. I. Measurement and modeling.
 AU Tsai, J.Y.; Canovai, C. (Dept. of Electr. & Comput. Eng., North Carolina State Univ., Raleigh, NC, USA); Osburn, C.M.; Wang, Q.F.; Rose, J.; Cowen, A.; Denker, M.S.
 SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer

Structures) (Jan.-Feb. 1994) vol.12, no.1, p.219-29. 46 refs.
 Price: CCCC 0734-211X/94/12(1)/219/11/\$1.00
 CODEN: JVTBD9 ISSN: 0734-211X
 Conference: Second International Workshop on the Measurement and Characterization of Ultra-Shallow Doping Profiles in Semiconductors.
 Research Triangle Park, NC, USA, 23-25 March 1993
 Sponsor(s): MCNC; NIST; American Vacuum Soc.; Office of Naval Res
 DT Conference Article; Journal
 TC Theoretical; Experimental
 CY United States
 LA English

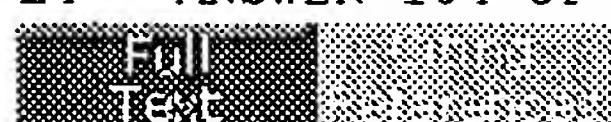
L4 ANSWER 102 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4649853 INSPEC DN B9406-2550F-004
 TI Secondary ion mass spectrometry measurements of shallow boron profiles in cobalt, silicon, and **cobalt disilicide**.
 AU Mohadjeri, B.; Svensson, B.G. (R. Inst. of Technol., Stockholm, Sweden)
 SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (Jan.-Feb. 1994) vol.12, no.1, p.209-13. 15 refs.
 Price: CCCC 0734-211X/94/12(1)/209/5/\$1.00
 CODEN: JVTBD9 ISSN: 0734-211X
 Conference: Second International Workshop on the Measurement and Characterization of Ultra-Shallow Doping Profiles in Semiconductors.
 Research Triangle Park, NC, USA, 23-25 March 1993
 Sponsor(s): MCNC; NIST; American Vacuum Soc.; Office of Naval Res
 DT Conference Article; Journal
 TC Theoretical; Experimental
 CY United States
 LA English

L4 ANSWER 103 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4636603 INSPEC DN A9409-6822-023; B9405-2550F-053
 TI Agglomeration-free nanoscale cobalt silicide film formation via substrate preamorphization.
 AU Pramanick, S.; Patnaik, B.K.; Rozgonyi, G.A. (Dept. of Mater. Sci. & Eng., North Carolina State Univ., Raleigh, NC, USA)
 SO Materials Reliability in Microelectronics III Symposium
 Editor(s): Rodbell, K.P.; Filter, W.F.; Frost, H.J.; Ho, P.S.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1993. p.475-80 of xi+496 pp. 8 refs.
 Conference: San Francisco, CA, USA, 12-15 April 1993
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 104 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1994:4619798 INSPEC DN A9408-8160B-023; B9404-2550F-028
 TI Kinetics of the formation of **cobalt disilicide** at high temperature under rapid electron beam heating.
 AU Warris, J.; Suleman, M. (Centre for Solid State Phys., Punjab Univ., Lahore, Pakistan); Mahmood, F.; Ahmed, H.
 SO Journal of Materials Science Letters (15 Jan. 1994) vol.13, no.2, p.96-8. 13 refs.
 CODEN: JMSLD5 ISSN: 0261-8028

DT Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 105 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1994:4599108 INSPEC DN A9406-6855-051
 TI Microstructural studies of epitaxial CoSi₂ layers on silicon produced by ion beam synthesis and rapid thermal annealing.
 AU Meekison, C.D.; Booker, G.R. (Dept. of Mater., Oxford Univ., UK); Reeson, K.J.; Spraggs, R.S.; Gwilliam, R.M.; Sealy, B.J.
 SO Journal of Applied Physics (15 Dec. 1993) vol.74, no.12, p.7129-33. 19 refs.
 Price: CCCC 0021-8979/93/74(12)/7129/5/\$6.00
 CODEN: JAPIAU ISSN: 0021-8979

DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 106 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1993:4531369 INSPEC DN A9401-6170A-003; B9401-2550B-008
 TI Annealing of silicon implanted by a high dose of cobalt ions investigated by in situ X-ray diffraction.
 AU Muller, M.; Bahr, D.; Press, W. (Inst. fur Experimentalphys., Kiel Univ., Germany); Jebasinski, R.; Mantl, S.
 SO Journal of Applied Physics (1 Aug. 1993) vol.74, no.3, p.1590-6. 27 refs.
 Price: CCCC 0021-8979/93/74(3)/1590/7/\$6.00
 CODEN: JAPIAU ISSN: 0021-8979

DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 107 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1993:4469978 INSPEC DN B9310-2560R-036
 TI Cobalt disilicide as dopant diffusion source for polysilicon gates in MOS devices.
 AU Lin, J.; Chen, W.; Banerjee, S.; Lee, J. (Microelectron. Res. Center, Texas Univ., Austin, TX, USA); Magee, C.
 SO Journal of Electronic Materials (June 1993) vol.22, no.6, p.667-73. 25 refs.
 CODEN: JECMAS ISSN: 0361-5235

DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 108 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1993:4463722 INSPEC DN A9318-6822-030; B9309-2550F-072
 TI Stability of nanoscale cobalt silicide film formation on polysilicon.
 AU Pramanick, S.; Erokhin, Yu.N.; Patnaik, B.K.; Rozgonyi, G.A. (North

Carolina State Univ., Raleigh, NC, USA); Gambino, J.P.
 SO Advanced Metallization and Processing for Semiconductor Devices and
 Circuits - II. Symposium
 Editor(s): Katz, A.; Murarka, S.P.; Nissim, Y.I.; Harper, J.M.E.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1992. p.435-40 of xvii+965 pp. 8
 refs.
 Conference: San Francisco, CA, USA, 27 April-1 May 1992
 Sponsor(s): AT&T Bell Lab.; A.G. Associates; Air Products & Chem.; et al
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 109 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1993:4463679 INSPEC DN B9309-2550F-054
 TI Thermal stability of cobalt disilicide for self-aligned silicide
 applications.
 AU Chen, W.; Lin, J.; Banerjee, S.; Lee, J. (Dept. of Electr. & Comput. Eng.,
 Texas Univ., Austin, TX, USA)
 SO Advanced Metallization and Processing for Semiconductor Devices and
 Circuits - II. Symposium
 Editor(s): Katz, A.; Murarka, S.P.; Nissim, Y.I.; Harper, J.M.E.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1992. p.163-7 of xvii+965 pp. 8
 refs.
 Conference: San Francisco, CA, USA, 27 April-1 May 1992
 Sponsor(s): AT&T Bell Lab.; A.G. Associates; Air Products & Chem.; et al
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 110 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

AN 1993:4383094 INSPEC DN A9310-6170T-007; B9305-2550B-034
 TI Dependence of buried CoSi₂ resistivity on ion implantation and annealing
 conditions.
 AU Namavar, F.; Kalkhoran, N.M.; Manke, J.M. (Spire Corp., Bedford, MA, USA);
 Luo, L.; McGinn, J.T.
 SO Phase Formation and Modification by Beam-Solid Interactions Symposium
 Editor(s): Was, G.S.; Rehn, L.E.; Follstaedt, D.M.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1992. p.285-92 of xix+913 pp. 13
 refs.
 Conference: Boston, MA, USA, 2-6 Dec 1991
 DT Conference Article
 TC Experimental
 CY United States
 LA English

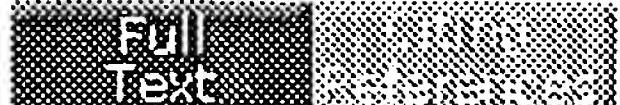
L4 ANSWER 111 OF 155 INSPEC (C) 2005 IEE on STN

FULL TEXT

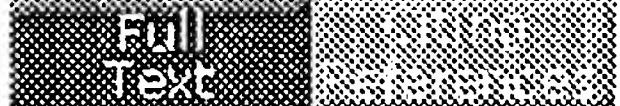
AN 1993:4337133 INSPEC DN A9306-6855-002; B9303-2550-016
 TI Improved stability of thin cobalt disilicide films using BF₂ implantation.
 AU Wang, Q.F.; Tsai, J.Y. (Dept. of Electr. & Comput. Eng., North Carolina
 State Univ., Raleigh, NC, USA); Osburn, C.M.; Chapman, R.; McGuire, G.E.
 SO Applied Physics Letters (14 Dec. 1992) vol.61, no.24, p.2920-2. 15 refs.
 Price: CCCC 0003-6951/92/492920-03\$03.00

CODEN: APPLAB ISSN: 0003-6951
 DT Journal
 TC Experimental
 CY United States
 LA English

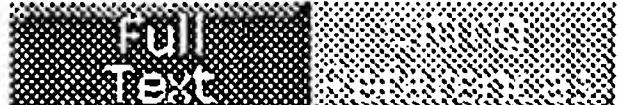
L4 ANSWER 112 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1992:4253694 INSPEC DN A9222-6855-027
 TI Stress measurements on vacuum evaporated cobalt silicide films on silicon substrates.
 AU Aloupojannis, P.; Travlos, A.; Papastaikoudis, C. (Inst. of Mater. Sci., Nat. Res. Centre, Demokritos, Athens, Greece); Hardtke, C.
 SO Vacuum (Aug. 1992) vol.43, no.8, p.807-9. 6 refs.
 Price: CCCC 0042-207X/92/\$5.00+.00
 CODEN: VACUAV ISSN: 0042-207X
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

L4 ANSWER 113 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1992:4151034 INSPEC DN A9212-6170W-006
 TI Shallow depth profiles of arsenic and boron in CoSi₂ measured by secondary ion mass spectrometry.
 AU Mohadjeri, B.; Svensson, B.G. (R. Inst. of Technol., Solid State Electron., Stockholm, Sweden)
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (Feb. 1992) vol.B64, no.1-4, p.654-8. 12 refs.
 Price: CCCC 0168-583X/92/\$05.00
 CODEN: NIMBEU ISSN: 0168-583X
 Conference: Ion Beam Analysis: Tenth International Conference. Eindhoven, Netherlands, 1-5 July 1991
 Sponsor(s): Eindhoven Univ. Technol.; Canberra Ind. Belgium; IBA-9
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 114 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1992:4085887 INSPEC DN A9206-7360D-001
 TI Quantum size effects and grain-boundary scattering in polycrystalline cobalt disilicide films.
 AU van der Kraan, R.G.P.; Jongste, J.F.; Jaeger, H.M.; Janssen, G.C.A.M.; Radelaar, S. (Inst. for Microelectronics & Submicron Technol., Delft Univ. of Technol., Netherlands)
 SO Physical Review B (Condensed Matter) (15 Dec. 1991) vol.44, no.23, p.13140-3. 17 refs.
 CODEN: PRBMDO ISSN: 0163-1829
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 115 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1992:4073992 INSPEC DN A9205-6822-004
 TI Grain boundary composition of pure and boron-doped **cobalt disilicide**.
 AU Malchere, A.; Gas, P. (Lab. de Metall., Fac. des Sci. et Tech. de St. Jerome, CNRS, Marseille, France); Haut, C.; Larere, A.; Nguyen, T.T.; Poize, S.
 SO Applied Surface Science (1991) vol.53, p.132-7. 25 refs.
 Price: CCCC 0169-4332/91/\$03.50
 CODEN: ASUSEE ISSN: 0169-4332
 Conference: 1991 European Workshop on Refractory Metals and Silicides.
 Saltsjobaden, Sweden, 24-27 March 1991
 Sponsor(s): Royal Inst. Technol. KTH; Swedish Board for Technol. Dev.,STU; Nordiska Balzers; et al
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 116 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1992:4069920 INSPEC DN A9204-6630F-001
 TI Cobalt lattice diffusion in bulk **cobalt disilicide**.
 AU Barge, T.; Poize, S.; Bernardini, J.; Gas, P. (Lab. de Metall., Fac. des Sci. et Tech. de St. Jerome, CNRS, Marseille, France)
 SO Applied Surface Science (1991) vol.53, p.180-5. 26 refs.
 Price: CCCC 0169-4332/91/\$03.50
 CODEN: ASUSEE ISSN: 0169-4332
 Conference: 1991 European Workshop on Refractory Metals and Silicides.
 Saltsjobaden, Sweden, 24-27 March 1991
 Sponsor(s): Royal Inst. Technol. KTH; Swedish Board for Technol. Dev.,STU; Nordiska Balzers; et al
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 117 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1992:4026840 INSPEC DN A9201-8115N-002
 TI **Cobalt disilicide** formed by rapid thermal annealing and through-metal arsenic implantation.
 AU Burte, E.P.; Min Ye (Fraunhofer-Arbeitsgruppe fur Integrierte Schaltungen, Erlangen, Germany)
 SO Journal of Materials Research (Sept. 1991) vol.6, no.9, p.1892-9. 16 refs.
 CODEN: JMREEE ISSN: 0884-2914
 DT Journal
 TC Experimental
 CY United States
 LA English

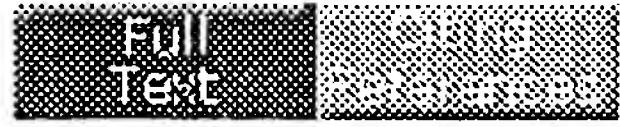
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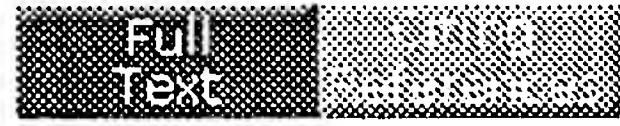
AN 1991:3964556 INSPEC DN A91116690
 TI **Cobalt disilicide** growth and interface structure analyses.
 AU D'Anterroches Meneau, C.; Perret, P. (CNET, CNS, Meylan, France)

SO Philosophical Magazine A (Physics of Condensed Matter, Defects and Mechanical Properties) (June 1991) vol.63, no.6, p.1221-39. 32 refs.
 Price: CCCC 0141-8610/91/\$3.00
 CODEN: PMAADG ISSN: 0141-8610
 DT Journal
 TC Experimental
 CY United Kingdom
 LA English

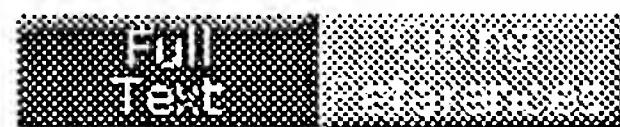
L4 ANSWER 119 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1991:3930791 INSPEC DN A91097835; B91049812
 TI Cobalt silicide formation caused by arsenic ion beam mixing and rapid thermal annealing.
 AU Min Ye; Burte, E.; Pei-Hsin Tsien; Ryssel, H. (Fraunhofer-Arbeitsgruppe fur Integrierte Schaltungen, Erlangen, Germany)
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (April 1991) vol.B55, no.1-4, p.773-7. 11 refs.
 Price: CCCC 0168-583X/91/\$03.50
 CODEN: NIMBEU ISSN: 0168-583X
 Conference: Eighth International Conference on Ion Implantation Technology (IIT-90). Guildford, UK, 30 July-3 Aug 1990
 Sponsor(s): IOP; Univ. Surrey
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 120 OF 155 INSPEC (C) 2005 IEE on STN

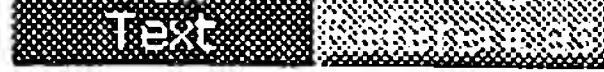

 AN 1991:3901505 INSPEC DN A91080782
 TI The structure of **cobalt disilicide** films formed on porous silicon in a solid-state reaction.
 AU Borisenko, V.E.; Bondarenko, V.P.; Raiko, V.A. (Minsk Radio Eng. Inst., Byelorussian SSR, USSR)
 SO Physics, Chemistry and Mechanics of Surfaces (1991) vol.6, no.4, p.935-45. 14 refs.
 CODEN: PCMSER ISSN: 0734-1520
 Translation of: Poverkhnost'. Fizika, Khimiya, Mekhanika. 14 refs.
 CODEN: PFKMDJ ISSN: 0207-3528
 DT Journal; Translation Abstracted
 TC Experimental
 CY USSR; United Kingdom
 LA English

L4 ANSWER 121 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1991:3853137 INSPEC DN A91048300
 TI Lattice diffusion of boron in bulk **cobalt disilicide**.
 AU Zaring, C.; Gas, P.; Svensson, B.G.; Ostling, M.; Whitlow, H.J. (Solid State Electron., R. Inst. of Technol., Stockholm, Sweden)
 SO Thin Solid Films (1 Dec. 1990) vol.193-194, no.1-2, p.244-7. 8 refs.
 Price: CCCC 0040-6090/90/\$3.50
 CODEN: THSFAP ISSN: 0040-6090
 Conference: 17th International Conference on Metallurgical Coatings and 8th International Thin Film Conference. San Diego, CA, USA, 2-6 April 1990

DT Conference Article; Journal
 TC Theoretical; Experimental
 CY Switzerland
 LA English

L4 ANSWER 122 OF 155 INSPEC (C) 2005 IEE on STN

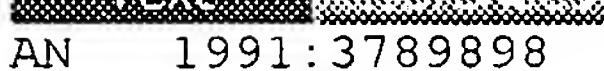
AN 1991:3848680 INSPEC DN A91048375
 TI Determination of the elastic constants of a **cobalt disilicide** intermetallic compound.
 AU Guenin, G. (Group d'Etudes de Metall. Phys. et Phys. des Materiaux, INSA, Villeurbanne, France); Ignat, M.; Thomas, O.
 SO Journal of Applied Physics (15 Dec. 1990) vol.68, no.12, p.6515-16. 10 refs.
 Price: CCCC 0021-8979/90/246515-02\$03.00
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 123 OF 155 INSPEC (C) 2005 IEE on STN

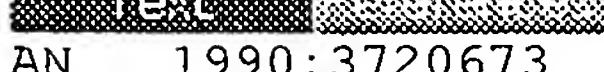
AN 1991:3841418 INSPEC DN A91042760
 TI Growth of cobalt and **cobalt disilicide** on Si(100).
 AU Gallego, J.M.; Miranda, R. (Dept. de Fisica de la Mater. Condensada, Univ. Autonoma de Madrid, Spain); Molodtsov, S.; Laubschat, C.; Kaindl, G.
 SO Surface Science (Dec. 1990) vol.239, no.3, p.203-12. 36 refs.
 Price: CCCC 0039-6028/90/\$03.50
 CODEN: SUSCAS ISSN: 0039-6028
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 124 OF 155 INSPEC (C) 2005 IEE on STN

AN 1991:3789898 INSPEC DN A91010500; B91001729
 TI The outdiffusion of boron and arsenic from pre-formed ion-beam-mixed **cobalt disilicide** layers using rapid thermal processing.
 AU Moynagh, P.B.; Brown, A.A.; Rosser, P.J. (STC Technol. Ltd., Harlow, UK)
 SO Rapid Thermal Annealing/Chemical Vapor Deposition and Integrated Processing Symposium
 Editor(s): Hodul, D.; Gelpey, J.C.; Green, M.L.; Seidel, T.E.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1989. p.261-6 of xi+494 pp. 5 refs.
 Conference: San Diego, CA, USA, 25-28 April 1989
 DT Conference Article
 TC Experimental
 CY United States
 LA English

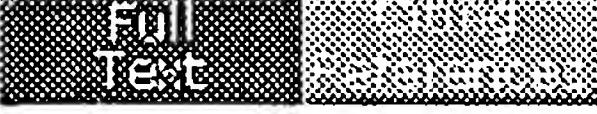
L4 ANSWER 125 OF 155 INSPEC (C) 2005 IEE on STN

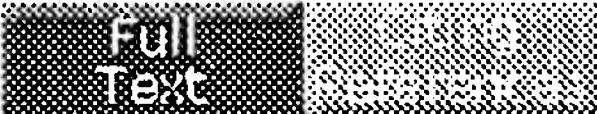
AN 1990:3720673 INSPEC DN A90132924
 TI Quantum transport in ultrathin CoSi₂ epitaxial films.
 AU DiTusa, J.F.; Parpia, J.M. (Lab. of Atomic & Solid State Phys., Cornell

Univ., Ithaca, NY, USA); Phillips, J.M.
 SO Applied Physics Letters (30 July 1990) vol.57, no.5, p.452-4. 27 refs.
 Price: CCCC 0003-6951/90/310452-03\$02.00
 CODEN: APPLAB ISSN: 0003-6951
 DT Journal
 TC Experimental
 CY United States
 LA English

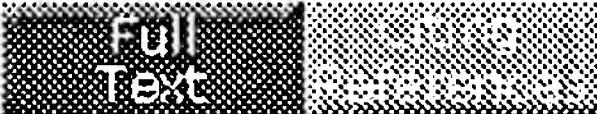
L4 ANSWER 126 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1990:3696196 INSPEC DN B90055272
 TI The outdiffusion of boron and arsenic from preformed cobalt disilicide layers.
 AU Moynagh, P.B.; Chew, C.P.; Affolter, K.B.; Rosser, P.J. (STC Technol. Ltd., Harlow, UK)
 SO ESSDERC '89. 19th European Solid State Devices Research Conference
 Editor(s): Heuberger, A.; Ryssel, H.; Lange, P.
 Berlin, West Germany: Springer-Verlag, 1989. p.248-52 of xxv+963 pp. 5 refs.
 Conference: Berlin, West Germany, 11-14 Sept 1989
 ISBN: 3-540-51000-1
 DT Conference Article
 TC New Development; Practical; Experimental
 CY Germany, Federal Republic of
 LA English

L4 ANSWER 127 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1990:3630180 INSPEC DN A90074455
 TI Arsenic redistribution during cobalt silicide formation.
 AU Pai, C.S.; Baiocchi, F.A.; Williams, D.S. (AT&T Bell Lab., Murray Hill, NJ, USA)
 SO Journal of Applied Physics (1 Feb. 1990) vol.67, no.3, p.1340-6. 20 refs.
 Price: CCCC 0021-8979/90/031340-07\$03.00
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 128 OF 155 INSPEC (C) 2005 IEE on STN


 AN 1990:3516486 INSPEC DN B90001378
 TI Resistivity of ion beam synthesised CoSi₂.
 AU Sealy, B.J.; Tan, B.L.; Gwilliam, R.M.; Reeson, K.J.; Jeynes, C. (Dept. of Electron. & Electr. Eng., Surry Univ., Guildford, UK)
 SO Electronics Letters (26 Oct. 1989) vol.25, no.22, p.1532-3. 15 refs.
 Price: CCCC 0013-5194/89/\$3.00+0.00
 CODEN: ELLEAK ISSN: 0013-5194
 DT Journal
 TC New Development; Practical; Experimental
 CY United Kingdom
 LA English

L4 ANSWER 129 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1990:3512394 INSPEC DN A90002787
 TI Effect of stress on the superconducting properties of CoSi₂ thin films.
 AU Briggs, A. (Centre de Recherches sur les Tres Basses Temp., CNRS,
 Grenoble, France); Chroboczek, J.; D'Avitaya, F.A.; Badoz, P.A.
 SO Thin Solid Films (July 1989) vol.174, p.285-8. 10 refs.
 Price: CCCC 0040-6090/89/\$3.50
 CODEN: THSFAP ISSN: 0040-6090
 Conference: 2nd International Symposium on Trends and New Applications in
 Thin Films (TATF 89). Regensburg, West Germany, 27 Feb-3 March 1989
 DT Conference Article; Journal
 TC Experimental
 CY Switzerland
 LA English

L4 ANSWER 130 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3500467 INSPEC DN A89142048; B89075612
 TI Formation of CoSi₂ on amorphous silicon by RTA.
 AU Drozdy, G.; Ronkainen, H.; Suni, I. (Semicond. Lab., Tech. Res. Center of
 Finland, Espoo, Finland)
 SO Applied Surface Science (Sept. 1989) vol.38, no.1-4, p.72-9. 9 refs.
 Price: CCCC 0169-4332/89/\$03.50
 CODEN: ASUSEE ISSN: 0169-4332
 Conference: European Workshop on Refractory Metals and Silicides.
 Houthalen, Belgium, 20-22 March 1989
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 131 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3496331 INSPEC DN A89135469
 TI Nucleation and growth of ultrathin epitaxial metal silicides on silicon.
 AU Batstone, J.L.; Tung, R.T.; Phillips, J.M.; Gibson, J.M. (AT&T Bell Labs.,
 Murray Hill, NJ, USA)
 SO Epitaxy of Semiconductor Layered Structures: Symposium
 Editor(s): Tung, R.T.; Dawson, L.R.; Gunshor, R.L.
 Pittsburgh, PA, USA: Mater. Res. Soc, 1988. p.253-8 of xiii+609 pp. 19
 refs. Availability: Clarke Associates - Europe, West Molesey, UK
 Conference: Boston, MA, USA, 30 Nov-4 Dec 1987
 ISBN: 0-931837-70-7
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 132 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3480094 INSPEC DN B89069128
 TI An improved self aligned silicide process for VLSI.
 AU Singh, A.; Khokle, W.S. (Semicond. Devices Area, CEERI, Raj, India)
 SO Microelectronics Journal (July-Aug. 1989) vol.20, no.4, p.11-17. 5 refs.
 CODEN: MICEB9 ISSN: 0026-2692
 DT Journal

TC Practical; Experimental
 CY United Kingdom
 LA English

L4 ANSWER 133 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3397248 INSPEC DN A89077031
 TI Two-step annealing for **cobalt disilicide** formation with lowest sheet resistance.
 AU Singh, A. (CEERI, Pilani, India)
 SO Physica Status Solidi A (16 Feb. 1989) vol.111, no.2, p.K191-3. 7 refs.
 CODEN: PSSABA ISSN: 0031-8965
 DT Journal
 TC Experimental
 CY German Democratic Republic
 LA English

L4 ANSWER 134 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3292181 INSPEC DN A89018812
 TI The diffusion of elements implanted in films of **cobalt disilicide**.
 AU Thomas, O.; Gas, P.; Charai, A.; LeGoues, F.K.; Michel, A.; Scilla, G.; d'Heurle, F.M. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)
 SO Journal of Applied Physics (15 Sept. 1988) vol.64, no.6, p.2973-80. 42 refs.
 Price: CCCC 0021-8979/88/182973-08\$02.40
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 135 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3290072 INSPEC DN B89009117
 TI Organometallic chemical vapor deposition of cobalt and formation of **cobalt disilicide**.
 AU Gross, M.E.; Schnoes Kranz, K.; Brasen, D.; Luftman, H. (AT&T Bell Labs., Murray Hill, NJ, USA)
 SO Journal of Vacuum Science & Technology B (Microelectronics Processing and Phenomena) (Sept.-Oct. 1988) vol.6, no.5, p.1548-52. 16 refs.
 Price: CCCC 0734-211X/88/051548-05\$01.00
 CODEN: JVTBD9 ISSN: 0734-211X
 DT Journal
 TC Application; New Development; Practical; Experimental
 CY United States
 LA English

L4 ANSWER 136 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3279033 INSPEC DN A89009140; B89000696
 TI Chemical vapor deposition of cobalt and formation of **cobalt disilicide**.
 AU Gross, M.E.; Schnoes, K.J. (AT&T Bell Labs., Murray Hill, NJ, USA)
 SO Proceedings of the Tenth International Conference on Chemical Vapor Deposition 1987

Editor(s): Cullen, G.W.; Blocher, J.M., Jr.
 Pennington, NJ, USA: Electrochem. Soc, 1987. p.759-65 of xvi+1269 pp. 14
 refs.
 Conference: Honolulu, HI, USA, Oct 1987
 Sponsor(s): Electrochem. Soc. Japan; Japan Soc. Appl. Phys
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L4 ANSWER 137 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3259408 INSPEC DN B88071466
 TI Formation and oxidation of implanted cobalt silicides on polycrystalline-silicon.
 AU Kozicki, M.N. (Coll. of Eng. & Appl. Sci., Arizona State Univ., Tempe, AZ, USA)
 SO 1988 Proceedings. Fifth International IEEE VLSI Multilevel Interconnection Conference (Cat. No.88CH2624-5)
 New York, NY, USA: IEEE, 1988. p.198-204 of 497 pp. 2 refs.
 Conference: Santa Clara, CA, USA, 13-14 June 1988
 Sponsor(s): IEEE
 Price: CCCC CH2624-5/88/0000-0198\$01.00
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 138 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3221686 INSPEC DN A88123847
 TI Diffusion of boron, phosphorus, and arsenic implanted in thin films of **cobalt disilicide**.
 AU Thomas, O.; Gas, P.; d'Heurle, F.M.; LeGoues, F.K.; Michel, A.; Scilla, G. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)
 SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1988) vol.6, no.3, pt.2, p.1736-9. 26 refs.
 Price: CCCC 0734-2101/88/031736-04\$01.00
 CODEN: JVTAD6 ISSN: 0734-2101
 Conference: 34th National Symposium of the American Vacuum Society.
 Anaheim, CA, USA, 2-6 Nov 1987
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 139 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3216715 INSPEC DN A88117560
 TI Electronic structure of **cobalt disilicide**.
 AU Newcombe, G.C.F.; Lonzarich, G.G. (Cavendish Lab., Cambridge Univ., UK)
 SO Physical Review B (Condensed Matter) (15 June 1988) vol.37, no.18, p.10619-22. 10 refs.
 CODEN: PRBMDO ISSN: 0163-1829
 DT Journal
 TC Experimental
 CY United States

LA English

L4 ANSWER 140 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3132953 INSPEC DN B88033165
 TI Technology for submicrometer Si/CoSi₂ epitaxial permeable-base transistor.
 AU Glastre, G.; Vincent, G.; Vareille, A.; Puissant, C.; Rosencher, E. (CNET, Meylan, France)
 SO IEEE Transactions on Electron Devices (Nov. 1987) vol.ED-34, no.11, p.2368. 0 refs.
 CODEN: IETDAI ISSN: 0018-9383
 Conference: 45th Annual Device Research Conference (papers in summary form only received). Santa Barbara, CA, USA, 22-24 June 1987
 Sponsor(s): IEEE
 DT Conference Article; Journal
 TC Application; Practical; Experimental
 CY United States
 LA English

L4 ANSWER 141 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3072104 INSPEC DN B88013176
 TI Self-aligned cobalt disilicide for gate and interconnection and contacts to shallow junctions.
 AU Murarka, S.P. (Rensselaer Polytech. Inst., Troy, NY, USA); Fraser, D.B.; Sinha, A.K.; Levinstein, H.J.; Lloyd, E.J.; Liu, R.; Williams, D.S.; Hillenius, S.J.
 SO IEEE Transactions on Electron Devices (Oct. 1987) vol.ED-34, no.10, p.2108-15. 28 refs.
 Price: CCCC 0018-9383/87/1000-2108\$01.00
 CODEN: IETDAI ISSN: 0018-9383
 DT Journal
 TC Application; New Development; Practical; Experimental
 CY United States
 LA English

L4 ANSWER 142 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3070490 INSPEC DN B88013004
 TI Stability of polycrystalline silicon-on-cobalt disilicide-silicon structures.
 AU Murarka, S.P. (Dept. of Mater. Eng., Rensselaer Polytech. Inst., Troy, NY, USA); Chang, C.C.; Adams, A.C.
 SO Journal of Vacuum Science & Technology B (Microelectronics Processing and Phenomena) (July-Aug. 1987) vol.5, no.4, p.865-9. 14 refs.
 Price: CCCC 0734-211X/87/040865-05\$01.00
 CODEN: JVTBD9 ISSN: 0734-211X
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 143 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1987:2928339 INSPEC DN A87077818; B87045893
 TI Silicon overgrowth on CoSi₂/Si(111) epitaxial structures: application to

permeable base transistor.

AU Arnaud d'Avitaya, F.; Chroboczek, J.A.; D'Anterroches, C.; Glastre, G.; Campidelli, Y.; Rosencher, E. (CNET, Meylan, France)

SO Journal of Crystal Growth (Feb. 1987) vol.81, no.1-4, p.463-9. 11 refs.
Price: CCCC 0022-0248/87/\$03.50
CODEN: JCRGAE ISSN: 0022-0248
Conference: Fourth International Conference on Molecular Beam Epitaxy.
York, UK, 7-10 Sept 1986
Sponsor(s): British Assoc. Crystal Growth

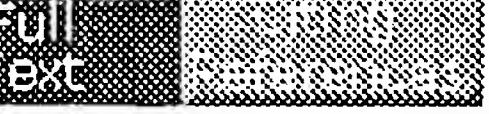
DT Conference Article; Journal

TC Experimental

CY Netherlands

LA English

L4 ANSWER 144 OF 155 INSPEC (C) 2005 IEE on STN



AN 1986:2745372 INSPEC DN A86112729
TI TiC as a diffusion barrier between Al and CoSi₂.
AU Appelbaum, A.; Murarka, S.P. (AT&T Bell Labs., Murray Hill, NJ, USA)
SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1986) vol.4, no.3, pt.1, p.637-40. 16 refs.
Price: CCCC 0734-2101/86/030637-04\$01.00
CODEN: JVTAD6 ISSN: 0734-2101
Conference: Proceedings of the 32nd National Symposium of the American Vacuum Society. Houston, TX, USA, 19-22 Nov 1985

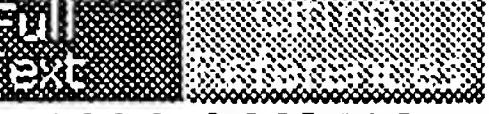
DT Conference Article; Journal

TC Experimental

CY United States

LA English

L4 ANSWER 145 OF 155 INSPEC (C) 2005 IEE on STN



AN 1986:2665412 INSPEC DN A86064334
TI Structural reactions of Si(111) with cobalt and formation of **cobalt disilicide**.
AU Wu, S.C.; Wang, Z.Q.; Li, Y.S.; Jona, F. (Coll. of Eng. & Appl. Sci., State Univ. of New York, Stony Brook, NY, USA); Marcus, P.M.
SO Physical Review B (Condensed Matter) (15 Feb. 1986) vol.33, no.4, p.2900-2. 13 refs.
CODEN: PRBMDO ISSN: 0163-1829

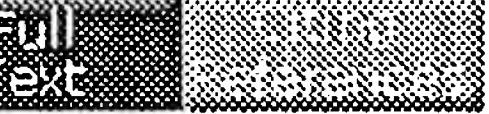
DT Journal

TC Experimental

CY United States

LA English

L4 ANSWER 146 OF 155 INSPEC (C) 2005 IEE on STN



AN 1986:2558436 INSPEC DN A86004817
TI Experimental investigations on the oxidation of **cobalt disilicide** (CoSi₂).
AU Kim, S.-J.; Banwell, T.C.; Shima, R.; Nicolet, M.-A. (Electr. Eng., California Inst. of Technol., Pasadena, CA, USA)
SO Proceedings of the SPIE - The International Society for Optical Engineering (1985) vol.530, p.152-8. 9 refs.
CODEN: PSISDG ISSN: 0277-786X
Conference: Advanced Applications of Ion Implantation. Los Angeles, CA, USA, 23-25 Jan 1985

DT Conference Article; Journal

TC Experimental
 CY United States
 LA English

L4 ANSWER 147 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2534170 INSPEC DN B85055791
 TI A Si permeable base transistor by metal/semiconductor hetero-epitaxy.
 AU Ishibashi, K.; Furukawa, S. (Tokyo Inst. of Technol., Yokohama, Japan)
 SO International Electron Devices Meeting. Technical Digest (Cat. No. 84CH2099-0)
 New York, NY, USA: IEEE, 1984. p.868-70 of 875 pp. 2 refs.
 Conference: San Francisco, CA, USA, 9-12 Dec 1984
 Sponsor(s): IEEE
 Price: CCCC CH2099-0/84/0000-0868\$01.00
 DT Conference Article
 TC New Development; Practical
 CY United States
 LA English

L4 ANSWER 148 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2455212 INSPEC DN A85066563
 TI Study of cobalt-disilicide formation from cobalt monosilicide.
 AU Appelbaum, A.; Knoell, R.V.; Murarka, S.P. (AT&T Bell Labs., Murray Hill, NJ, USA)
 SO Journal of Applied Physics (15 March 1985) vol.57, no.6, p.1880-6. 18 refs.
 Price: CCCC 0021-8979/85/061880-07\$02.40
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 149 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2425224 INSPEC DN A85038646; B85022525
 TI Cospattered cobalt silicides on silicon, polycrystalline silicon, and silicon dioxide.
 AU Murarka, S.P.; Vaidya, S. (AT&T Bell Labs., Murray Hill, NJ, USA)
 SO Journal of Applied Physics (15 Dec. 1984) vol.56, no.12, p.3404-12. 20 refs.
 Price: CCCC 0021-8979/84/243404-09\$02.40
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Practical; Experimental
 CY United States
 LA English

L4 ANSWER 150 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2415980 INSPEC DN A85039373
 TI Cobalt disilicide: crystal growth and physical properties.
 AU Ditchek, B.M. (GTE Labs., Waltham, MA, USA)
 SO Journal of Crystal Growth (Nov. 1984) vol.69, no.1, p.207-10. 13 refs.

Price: CCCC 0022-0248/84/\$03.00
 CODEN: JCRGAE ISSN: 0022-0248

DT Journal
 TC Experimental
 CY Netherlands
 LA English

L4 ANSWER 151 OF 155 INSPEC (C) 2005 IEE on STN

FILE **TEXT**

AN 1984:2250876 INSPEC DN A84061844
 TI Cobalt disilicide epitaxial growth on the silicon (111) surface.
 AU Pirri, C.; Peruchetti, J.C.; Gewinner, G. (Inst. des Sci. Exactes et Appliquees, Univ. de Haute-Alsace, Mulhouse, France); Derrien, J.
 SO Physical Review B (Condensed Matter) (15 March 1984) vol.29, no.6,
 p.3391-7. 38 refs.
 CODEN: PRBMDO ISSN: 0163-1829
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 152 OF 155 INSPEC (C) 2005 IEE on STN

FILE **TEXT**

AN 1983:1984454 INSPEC DN A83014753; B83007325
 TI Thermal oxidation of cobalt disilicide.
 AU Bartur, M.; Nicolet, M.-A. (California Inst. of Technol., Pasadena, CA,
 USA)
 SO Applied Physics A (Solids and Surfaces) (Oct. 1982) vol.A29, no.2,
 p.69-70. 9 refs.
 Price: CCCC 0721-7250/82/0029/0069/\$01.00
 CODEN: APSFDB ISSN: 0721-7250
 DT Journal
 TC Experimental
 CY Germany, Federal Republic of
 LA English

L4 ANSWER 153 OF 155 INSPEC (C) 2005 IEE on STN

FILE **TEXT**

AN 1983:1974116 INSPEC DN A83008343
 TI Direct determination of atomic structure at the epitaxial cobalt disilicide on (111) Si interface by ultrahigh resolution electron microscopy.
 AU Gibson, J.M.; Bean, J.C.; Poate, J.M.; Tung, R.T. (Bell Labs., Murray Hill, NJ, USA)
 SO Applied Physics Letters (1 Nov. 1982) vol.41, no.9, p.818-20. 7 refs.
 Price: CCCC 0003-6951/82/090818-03\$01.00
 CODEN: APPLAB ISSN: 0003-6951
 DT Journal
 TC Experimental
 CY United States
 LA English

L4 ANSWER 154 OF 155 INSPEC (C) 2005 IEE on STN

FILE **TEXT**

AN 1970:202621 INSPEC DN A70078791
 TI Thermal and electrical conductivity of cobalt disilicide.

AU Krentsis, R.P.; Ostrovskii, F.I.; Frolov, A.A.; Gel'd, P.V.
SO Izvestiya Vysshikh Uchebnykh Zavedenii, Fizika (1970) no.8, p.157-8
CODEN: IVUFAC ISSN: 0021-3411
Translation in: Soviet Physics Journal
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AN 1969:5639 INSPEC DN A69003480
TI Solid solutions of disilicides of nickel and cobalt.
AU Sidorenko, F.A.; Miroshnikov, L.A.; Gel'd, P.V.
SO Izvestiya Vysshikh Uchebnykh Zavedenii, Fizika (1968) no.5, p.70-5
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